



### **About ATP**

Since 1991, we have consistently distinguished ourselves as one of the world's leading original equipment manufacturers (OEM) of high-performance, high-quality and high-endurance NAND flash products and DRAM modules. As a manufacturing leader, we provide memory and storage solutions trusted by diverse industries that require high levels of technical proficiency, manufacturing quality, and wide operating temperature ranges.

We reinforce our leadership by continuing to blaze the trail as:

## The Global Leader in Specialized Storage and Memory Solutions

ATP-developed firmware and mass production infrastructure are fully capable of addressing any variety of embedded/ industrial usage cases. We can provide specialized configurations to support unique memory and storage requirements, all with the aim of delivering best total cost of ownership (TCO) for our customers.

#### The Thermal Experts in Storage and Memory Solutions

We are widely known as one of the first to develop industrial-temperature (I-Temp) 3D NAND flash storage for extreme operating conditions. This expertise continues to this day as customizable thermal solutions are made available for the latest NVMe modules that run at blistering speeds. Through constant collaboration with customers, as well as our top-notch firmware and hardware engineering capabilities, we make sure that optimal sustained performance is achieved despite freezing cold or blazing hot temperatures.

#### A True Manufacturer

We manage every stage of the manufacturing process to ensure quality and product longevity, offering in-house design, testing, and tuning from integrated circuits (ICs) to module and drive level. All products are meticulously tested and validated before leaving our manufacturing facilities to make sure that they comply with the strictest industry standards and that they will operate reliably under rugged conditions and workloads for a long time.

#### ATP USA

SAN JOSE, CA, USA

#### ATP EUROPE

MUNICH, GERMANY

ATP CHINA SHANGHAI, CHINA

#### ATP JAPAN

TOKYO, JAPAN

## ATP HEADQUARTERS TAIPEI, TAIWAN

## **Table of Contents**

About ATP	2	DRAM SOLUTIONS	26
President's Message	3	DDR5	30
The Global Leader in Specialized	4	Longevity Program	32
Storage and Memory Solutions		Complete DRAM Portfolio	33
Exclusive Inside Peek:			
ATP as True Manufacturer	6	FLASH SOLUTIONS	34
Key Manufacturing Processes	7	Solid State Drives and Modules	35
Certifications, Associations and Compliances	8	Memory Cards	46
Segment Challenges and Solutions	9	Managed NAND	52
Thermal Solutions	14		32
Endurance Solutions	18	Flash Products Naming Rule	55
Security Solutions	21	Solutions & Technologies	56
CFexpress & USB 3.0	23	Flash Technology Overview table	59
Value Line SSDs	24	Complete Flash Spec Overview &	60
ATP DDR5	25	Product Dimensions	



In now over 30 years in the memory business, we have maintained two key principles in how we work:

- 1) Deeply understand our value to you, our customers, partners, and suppliers.
- 2) Continuously adapt, learn, and improve while maintaining focus on core competencies.

These principles have been manifested into our team's execution over the years and are now finally expressed via our "We Build With You" mantra, which can be interpreted in the more literal sense as our strength in specialty product customization by project, or in the grander scheme as learning and growing collaboratively over the years with our customers, partners, and suppliers.

Today, we proudly state with confidence that we are ready for any specialty requirement that comes our way, and back that up with industry-leading quality and service.

Over the next several years, we will not only be continuing our journey to bring value to customers but will also endeavor to scale this to be more efficient and to span across every industry segment we touch. We will apply project-specific lessons learned and capabilities and scale these values segment wide. We will be more aggressive in sharing these values and improvements with all of you, and hope that you will see this speed up our collaborations.

You can expect to have more focused project proposals backed up with years of experience in the related product or application. You will see more application/segment-specific product roadmaps and data sheets specifically addressing the pain points and feature sets most relevant to your application area.

In this way, our over 30 years of experience are not only applied into our capability to customize to your requirements, but also into the collaborative process to be smoother and more efficient. We believe that through ongoing technology changes, increasing usage case diversity, and the many global macro influences these few years, we can continue to grow and succeed in our business together.

ATP has recently finalized plans and broken ground on a new manufacturing facility in southern Taiwan. Armed with the latest in energy, water, and air circulatory infrastructure, the new facility is designed from the ground up for industry-leading green sustainable manufacturing. In the coming months, you can expect to hear more about improvements in efficiency due to the application of the latest in automation and smart factory technologies.

Let me take this opportunity to thank all of you for your unwavering friendship, support, and partnership. The ATP team is looking forward to the next stage and our next project with you.

We Build With You.

**Jeff Hsieh**President

# THE GLOBAL LEADER IN SPECIALIZED STORAGE AND MEMORY SOLUTIONS

One size does not fit all. Providing Unique Solutions for Unique Challenges.

We at ATP recognize the uniqueness of each customer's requirements, so we go the extra mile to custom-configure our memory and storage solutions according to the needs of our customers.

#### Adding Value to Optimize TCO

We want to offer our customers an opportunity to stand out in the market, optimize investments, and add value without incurring huge costs.

### Sustaining Competitiveness

Due to ATP's advanced manufacturing capabilities and control of the supply chain as a true manufacturer, we can provide specialized solutions for specific needs while maintaining competitiveness in unit cost.

#### Pillars of ATP Customization & Services



#### THERMAL

With a variety of customer host environments in terms of sustained temperature, cross temperature, and air flow, ATP custom-configures firmware and hardware to manage the best balance of performance and device life span.



#### **ENDURANCE**

ATP's experience dealing with a wide scope in workload models allow for custom set configurations, tailor-fitted to customer's requirements meeting the best compromise in terms of cost per GB, DWPD, and performance.





#### **SECURITY**

A wide range of optional custom security technologies provide extra layers of protection safeguarding data at rest and in transit.



#### **LONGEVITY**

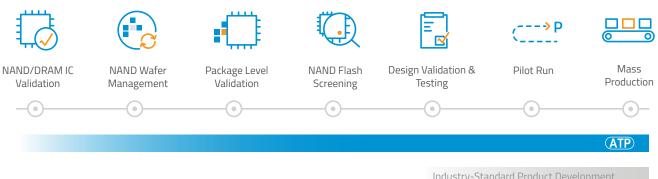
Long product cycles with a 5-year roadmap, support for legacy memory products, and controlled BOM with PCN/EOL notice typically 6 months in advance ensure consistent quality and supply availability.

## ATP Delivers Specialized Storage and Memory Products with Own-Developed Firmware and Mass Production Infrastructure

As a true manufacturer, ATP is in charge of all the stages of the manufacturing process. This makes ATP totally capable of developing customizable firmware and mass production infrastructure to meet the thermal, security, endurance, and other requirements of customers. Such specialized configurations can address any variety of embedded and industrial use cases.

This once again demonstrates ATP's commitment to deliver optimal total cost of ownership (TCO) value for its customers as storage demands of the Industrial Internet of Things (IIoT), edge computing, and other high-reliability applications continue on the upsurge.

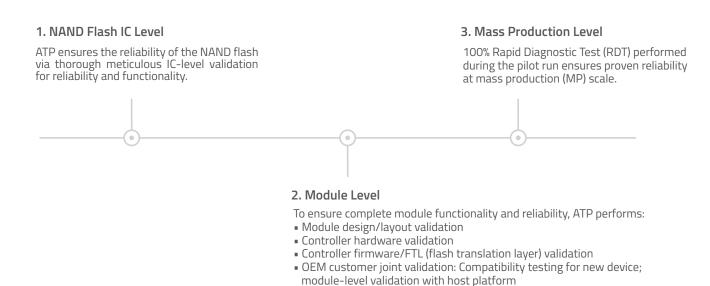
The following figure shows ATP's quality journey beginning with the very basic component level, the ICs, which serve as the building blocks of all ATP products.



Industry-Standard Product Development

#### Three Stages of ATP's Complete Process Ownership

All DRAM and flash storage products go through a series of functional and reliability tests to ensure that they match the specifications agreed upon by ATP and the customer and to ensure that they are compatible with host environments.



#### **Key Manufacturing Processes**

ATP demonstrates its extensive expertise in the use of NAND wafer through its own packaging capabilities to deliver IC/package-level field support and extended support for legacy products.



#### SiP Process

Integrates components within a single package. ATP's SiP process encapsulates all exposed components to provide protection and shielding.



#### **Surface Mount Technology**

ATP's SMT process includes mandatory 100% Solder Paste Inspection (SPI) In-Line System, which is optional for other manufacturers. ATP's  $N_2$  Reflow effectively limits the amount of oxygen to prevent oxidation in components during the heating process by pumping nitrogen into the reflow chamber. It also improves solder wetting, which allows the metal in the solder (in the form of molten fluid) to adhere properly to the components for optimal solder joint.



### **Our Corporate Responsibility Commitment**



#### Certifications

According to leading industry standards











ISO 9001:2015

ISO 14001:2015

ISO45001:2018

ISO14064-1:2018

ISO 17025







VDA 6.3

IATF 16949 (LOC)

Sony **Green Partner** 

ATP has extensive product validation experience in industry-specific standards, including:

- AEC-Q100
- IEC 60529
- JESD22-A110
- JESD78B

- SNIA
- IP6X ATIS
- MIL-STD-883
- UL94-v0

- JESD219
- IEC 61000-4-2:2008

### **Industry Associations and Compliances**































## All-Terrain Automotive Storage Solutions for the Road Ahead

ATP Electronics leverages 30 years of manufacturing experience and a decade of automotive expertise to provide best-in-class automotive-grade memory and storage solutions.

The world's leading OEM/Tier 1 suppliers, system developers and service providers trust ATP to deliver the highest levels of data accuracy, consistency and integrity for the most demanding automotive applications.

#### Up to Speed with EV & Vehicle Data Logging NAND Flash Storage Requirements

Next-generation electric vehicles require fast, reliable, and robust data storage media, not only for navigation and infotainment systems, but also for advanced applications to ensure riding safety and comfort. Vehicle data logging systems collect real-time sensor data from radar/lidar/telematic systems over long periods of time for prototype vehicles. ATP NAND flash storage products come in compact packages with high density, superior read/write performance, and customizable thermal management solutions, making them ideal solutions for constrained spaces and rugged operating environments.

#### Why the Automotive World Trusts ATP



## Automotive Quality System Qualified, Certified and Recognized

Compliance with the most stringent international quality standards

### International Automotive Task Force (IATF) 16949

Defines the quality management system requirements for the design, development, production and, when relevant, installation, and service of automotive-related products.

#### VDA 6.3

Defines a process-based audit standard for production parts and services to evaluate and improve controls in a manufacturing organization.

## International Material Data System (IMDS)

A global archive of information on all materials found in finished automobile manufacturing.



## Automotive Compliance and Standards

Always Ready for the Rough Road

#### AEC-Q100\*

- e.MMC: -40°C to +105°C (Grade 2), -40°C to +85°C (Grade 3) ambient operating temperature range
- SD/microSD: Selected AEC-Q100 and AEC-Q104 test items; -40°C to +85°C (Grade 3) ambient operating temperature range
- \* Selected AEC-Q100 test items and conditions approved by customers. May vary by product and project support.

#### International Protection Marking\*

- Waterproof (IPX7)
- Dustproof (IP6X/IP5X)
- \* For SD/microSD cards only.



#### **Longevity Commitment**

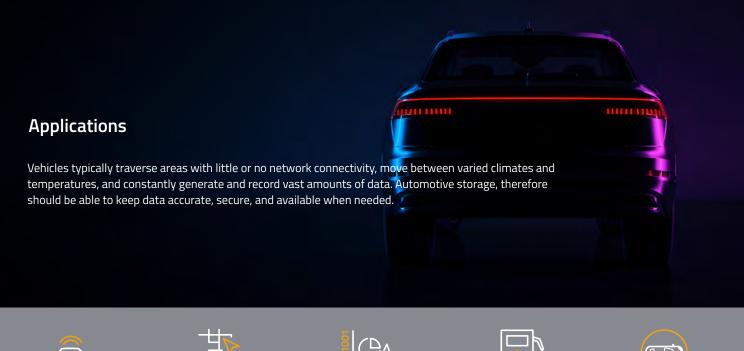
Your Partner for the Long Haul

## Controlled BOM with PCN/EOL Notice\*

- Long product cycles with buffer inventory
- Any changes affecting the process or product are communicated to customers
- 5-year roadmap
- PCN/EOL notice typically 6 months in advance
- \* May vary by product and project support.

#### Global and Local FAE Support

- Over 100 engineers and technical staff worldwide
- Global presence in five countries with support sales and service offices
- Global and regional franchised distributors









IV









Drive Recorder

#### **Automotive Storage Portfolio**

Form Factor	Product Line Naming	Interface	Recommended Capacity	NAND	NAND Reliability TBW (max)*		Performance up to)	Operating Temperature (°C)	
						Read	Write		
M.2 2280	N600Si / Sc	PCIe G4 x4	240 GB to 3.84 TB	3D TLC	11,400	6,450	6,000	-40 to 85 / 0 to 70	
IVI.2 2200	N600Si / Sc	PCIe G3x4	120 GB to 3.84 TB	3D TLC	10,600	3,420	3,050	-40 to 85 / 0 to 70	
U.2	N600Si / Sc	PCIe G4 x4	960 GB to 7.68 TB	3D TLC	22,800	3,900	3,800	-40 to 85 / 0 to 70	
0.2	N600Si	PCIe G3x4	960 GB to 7.68 TB	3D TLC	21,000	3,100	1,400	-40 to 85	
	S600Sia / Sca	UHS-I	8 GB to 16 GB	MLC	19	68	23	-40 to 85 / -25 to 85	
SD/	S600Sia / Sca	UHS-I	32 GB to 64GB	3D TLC (Longevity)	116	96	35	-40 to 85 / -25 to 85	
SDHC/ SDXC	S650Sc / Si	UHS-I	32 GB to 64GB	3D TLC (High Endurance)	291	96	29	-40 to 85 / -25 to 85	
	S600Sc / Si	UHS-I	64 GB to 256 GB	3D TLC (Low Latency)	698	96	65	-25 to 85 / -40 to 85	
	S600Si / Sc	UHS-I	32 GB to 64GB	3D TLC (Longevity)	116	96	35	-40 to 85 / -25 to 85	
microSD/ microSDHC/	S650Si / Sc	UHS-I	32 GB to 64GB	3D TLC (High Endurance)	291	96	29	-40 to 85 / -25 to 85	
microSDXC	S600Si / Sc	UHS-I	32 GB to 256 GB	3D TLC (Low Latency)	698	96	65	-40 to 85 / -25 to 85	
	E700Paa	v5.1, HS400	8 GB to 64 GB	3D MLC (pSLC mode)	1,213	300	240	-40 to 105 (AEC-Q100 Grade 2)	
- MMC	E600Saa	v5.1, HS400	16 GB to 128 GB	3D MLC	309	300	170	-40 to 105 (AEC-Q100 Grade 2)	
e.MMC	E700Pia	v5.1, HS400	8 GB to 64 GB	3D MLC (pSLC mode)	1,320	300	240	-40 to 85 (AEC-Q100 Grade 3)	
	E600Sia	v5.1, HS400	16 GB to 128 GB	3D MLC	824	300	170	-40 to 85 (AEC-Q100 Grade 3)	

 $<sup>^{*}</sup>$  Under highest Sequential write value. May vary by density, configuration and applications.

### Networking / Telecom

High-speed networks provide the connectivity that feeds the growing appetite for digital communications. At the edge, requirements for higher memory and NAND flash storage specifications are growing to address environmental and performance challenges as 5G, Mobile Edge Computing (MEC) and Open Radio Access Network (O-RAN) transform the topology and architecture of communication networks.

Meanwhile, cybersecurity continues to pose numerous challenges, data centers are experiencing exponential expansions, and software-defined wireless area networking (SD-WAN) keeps evolving to offer benefits and capabilities.

With its growing memory and NAND flash storage requirements, the networking and telecommunications industry continues to trust ATP Electronics as it did over three decades ago. Today, over 70% of companies listed on Gartner's Magic Quadrant report for Primary Storage, Data Center and Cloud Computing, and WAN-Edge Infrastructure consider ATP as a strategic supplier.



5G/O-RAN/MEC



Cybersecurity/NGFW/ Networking



Data Center



SD-WAN

Unique Challenges	Solutions
Embedded form factors for boot/cache drives	SSDs with power loss protection:  SATA: M.2 2280/2242, mSATA, 2.5", CFast  NVMe: M.2 2280/2230, HSBGA
Need to maintain BOM consistency for long lifetime	5 years+ longevity and BOM control
Data integrity/reliability	End-to-end data path protection – CRC, SRAM/DRAM/NAND ECC, NAND RAID
Wide ambient temperature support	<ul> <li>Industrial temperature operation</li> <li>High/Low temperature reliability validation</li> <li>Thermal cycling validation</li> <li>Thermal vs. Performance characterization &amp; solutioning</li> <li>Heatsink solutions</li> </ul>
High Read and Write endurance (TBW/DWPD)	High-endurance 3D TLC/pSLC/SLC series Capacity overprovisioning settings
Sustained write throughput	Configuration optimization - NAND mode selection, cache tuning, overprovisioning settings, firmware tuning
Surprise power loss or glitch	<ul><li>MCU-based power loss protection (PLP)</li><li>Customized power cycling tests</li><li>Sudden Power-Off Recovery (SPOR) by firmware</li></ul>
Data Security	<ul><li>AES, TCG-Opal 2.0, Self-Encrypting Drive</li><li>Secure Erase</li><li>Customized encryption security</li></ul>
Environmental and safety homologation	Global certifications:  FCC, CE, UKCA, VCCI, BSMI, KCC, RCM, IC, UL, CB, CSA, Morocco, etc. (optional)  ROHS, REACH
Customized validation	Collaboration on customer specific test, qualification, and validation that are beyond JEDEC standards  Ex: Performance/Latency, Power consumption, Endurance, Data Retention 4 Corner power cycling and thermal testing, Signal Integrity, system interoperability, reliability testing, etc.

Note: Listed ATP solutions are provided for reference only and may change without notice. Contact an ATP Distributor or Representative in your area to discuss how ATP can meet your specific requirements.









Automation/ Industrial 4.0/Drones



Energy



Gaming



Test & Measurement

Unique Challenges	Solutions
Embedded form factors for legacy platforms	<ul> <li>512 MB to 8 GB SLC/pSLC/MLC microSD, SD</li> <li>Industrial M.2 SATA3 or NVMe, mSATA, CF, CFast, eUSB, UFD, e.MMC, BGA SSD</li> <li>DDR2/DDR3 VLP, 1.35V</li> </ul>
Need to maintain BOM consistency for long lifetime	5 years+ longevity and BOM control
Wide ambient temperature Fanless platforms	<ul> <li>Extreme temperature solution (-40°C to 105°C)</li> <li>High/low temperature reliability validation</li> <li>Thermal cycling validation</li> <li>Thermal vs. Performance characterization &amp; solutioning</li> <li>Heatsink solutions</li> <li>I-Temp RCD</li> </ul>
High endurance for least maintenance (low cost of ownership)	High-endurance SLC/pSLC/3D TLC series Capacity overprovisioning settings
Surprise power loss or glitch	<ul> <li>MCU-based hardware power loss protection (PLP)</li> <li>Customized power cycling tests</li> <li>Sudden Power-Off Recovery (SPOR) by firmware</li> </ul>
Environmental erosion prevention	<ul> <li>30 to 50µ" gold fingers by customization</li> <li>SIP package waterproof IP67</li> <li>Anti-erosion, salt fog testing</li> <li>Conformal coating (optional)</li> </ul>
Customized FW setting	<ul> <li>Card speed mode</li> <li>Write capable, Read privilege control</li> <li>Boot-up mechanism tuning</li> <li>SMART ID attributes tuning</li> </ul>
Customized validation/Label	Collaboration on customer specific test, qualification, and validation that are beyond JEDEC standards

Note: Listed ATP solutions are provided for reference only and may change without notice. Contact an ATP Distributor or Representative in your area to discuss how ATP can meet your specific requirements.

## Transportation

Transportation plays a vital role in supply chain management; hence, the timely delivery of goods and services can be a daunting challenge. Data technologies, artificial intelligence (AI), and other technological advancements are allowing transportation systems to operate more efficiently at optimal costs while also delivering better services. At the heart of these advancements are memory and data storage solutions that enable better fleet management, predictive analytics, and smart logistics.









Railway



Transportation Infrastructure

Unique Challenges	Solutions
Legacy form factors required	<ul> <li>CF/CFast cards, low-density micro/SD cards</li> <li>eUSB, UFD</li> <li>mSATA</li> <li>e.MMC</li> <li>DDR3 DRAM</li> </ul>
Lengthy development cycle	<ul><li>5 years+ longevity and BOM/FW control</li><li>Special extension support</li></ul>
High ambient temperature	<ul><li>Industrial/Automotive Grade temp (AG2 &amp; 3)</li><li>Tailored thermal solutions</li></ul>
Zero-failure safety standard	<ul><li>High-endurance SLC/pSLC/MLC/TLC series</li><li>Customized spare block (OP) setting</li></ul>
Unstable power supply from the platform	<ul> <li>Customized power cycling test</li> <li>Sudden Power-Off Recovery (SPOR) by firmware (FW) enhancement</li> <li>MCU-based power loss protection (PLP)</li> </ul>
Environmental erosion prevention	<ul> <li>50μ" gold fingers by customization</li> <li>Waterproof system-in-package (SIP)</li> <li>Anti-erosion, salt fog testing</li> </ul>
Host device power-on/off patterns	■ Firmware adjustment on CMD and cache behaviors

Note: Listed ATP solutions are provided for reference only and may change without notice. Contact an ATP Distributor or Representative in your area to discuss how ATP can meet your specific requirements.

## ATP Customizable Thermal Management Solutions: Steady Wins the Race

In this increasingly data-centric era, industrial applications are constantly generating data requiring storage and quick access; however, we are in a constant race not only against time, but also against heat.

NVMe solid state drives (SSDs) deliver blazing-fast performance, running at four to six times the speed of Serial ATA (SATA), but their blistering speeds, exacerbated by extreme temperature variations and constricted embedded environments with little to no ventilation, can lead to heating issues that can compromise the stability of the storage device.



#### How can NVMe SSDs beat the heat?

While most of the storage world is saying, "The faster the better," ATP is taking the "Steady wins the race" stance, ensuring that blazing fast does not turn to blazing hot.

The ATP approach to thermal management may be likened to running a marathon. We consider the following aspects:

- Environmental Assessment. Similar to checking environmental factors, such as the weather and road conditions, we first check the airflow within the system. Is the airflow enough to provide cooling, especially for fan-less systems?
- Physical Conditions. Next, we assess heat dissipation by looking at the "racetrack" which is the physical and mechanical design of the system. Considering the available space, what is the ideal heatsink solution and what material should be used? Will components on the printed circuit board (PCB) cause mechanical interference with the heatsink?
- Ambient Simulation. The ATP-built mini chamber is used to test the SSD within a controlled test environment, with a temperature test range from 25°C to 85°C. The mini chamber simulates and adjusts thermal environments based on customer's profile.
- Suitable Gear/Equipment. Selecting the suitable gear for a race can make a huge difference. What you wear keeps you cooler. The same is true in thermal management. Choosing a heatsink with excellent conductivity, reliability, design and hardness can help determine the success of the heatsink solution and may impact the total cost of ownership (TCO).
- Pacing Strategy. Managing heat while keeping performance optimized is a big challenge. The ATP Dynamic Thermal Throttling mechanism provides a delicate balance between performance and temperature by continuously detecting device temperature and adjusting the pace.

Steady wins the race!



When the composite temperature keeps increasing, the SSD repeatedly slows down to cool it. The 8 mm heatsink can dissipate heat complemented by airflow support.

The maximum composite temperature of NVMe SSD is reduced, and the performance is steady with optimized FW algorithm.

## The ATP Solution Simulation and Customization: One Scenario Does Not Fit All

Each customer faces a unique thermal challenge, which could be an interplay of all the factors mentioned.

As a global leader in customization, ATP recognizes the unique thermal challenges for different use cases and scenarios, and thus offers holistic and customizable solutions that combine firmware and hardware technologies to meet customers' specific thermal requirements.

ATP provides simulation and customization options depending on project and according to customers' request. The following table shows available heatsink solutions.

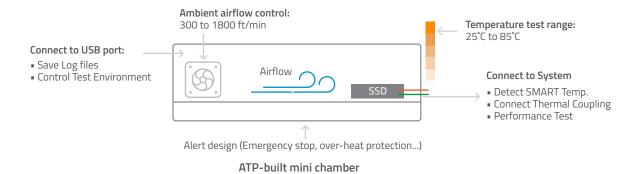
		Heat Dissipation Solu	tions				
Form Factor supported		M.2 2280		U.2			
Type	Copper Foil	4 mm Fin-Type Heatsink	8 mm Fin-Type Heatsink	15 mm Fin-Type Housing			
Dimensions: L x W x H (mm)	80 x 22 x 3.9	80 x 24.4 x 8.3	80 x 24.4 x 12.3	100.5 x 69.85 x 15			
Material	Copper	Upper: Aluminum alloy Bottom: Stainless steel	Upper: Aluminum alloy Bottom: Stainless steel	Aluminum alloy			
Suitability	Limited space	Enough space for effective heat dissipation					
Fixedness	Stick	Clips	Clips design				

## ATP Simulation Strategy: Testing Under Worst-Case Scenario to Determine Sufficient Cooling Solutions

Simulation is an important aspect of the manufacturing process. It allows ATP to test and validate its thermal solutions under different conditions and challenges in controlled environments.

ATP combines both hardware and software simulation in its three-pronged simulation testing strategy for thermal solutions:

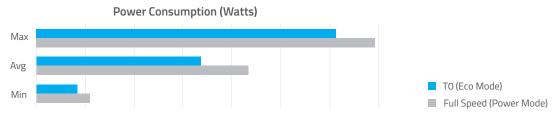
- Component-Level Simulation. This is a pure hardware simulation based on full-speed operation, which is the worst-case scenario, to determine heat distribution in each PCB layer. Components using cooling solutions are subjected to high temperatures to test heat distribution efficiency considering various factors such as ambient temperature, airflow, thermal resistance, and power consumption of main components.
- System-Level Simulation. The Cadence® simulation software can run system/module-level simulation. By providing contrasting results for scenarios with or without thermal solution, the simulation software demonstrates the efficiency of ATP heatsinks under worst-case ambient and airflow conditions.
- ATP-Built Mini Chamber. The proprietary ATP-built mini chamber to simulates and adjusts thermal environments based on customer's profile. The mini chamber can run a real SSD test by simply connecting to a system's USB port.



#### ATP Optimization Strategy: Steady Wins the Race

The ATP Dynamic Thermal Throttling is a firmware-based mechanism that prevents extreme temperature increase by continuously detecting device temperature. As the mechanism balances performance and temperature, Eco Mode is triggered, resulting in lower power consumption.

The following figure shows that power consumption is significantly reduced under Eco Mode.



## Flagship M.2, U.2 SSDs with PCle Gen 4 x4 Interface Offer Excellent R/W Performance for High-Performance Applications

Fastest PCIe Generation Cuts Latency, Doubles Gen 3 Data Rate

ATP's latest flagship offerings, the new N600Si/Sc NVMe M.2 2280 and U.2 SSDs, sport the PCle Gen 4 x4 interface to meet the growing need for high-speed data transfer in today's demanding applications. With twice the bandwidth of the previous generation (8 GT/s), PCle Gen 4's 16 GT/s data rate translates to a bandwidth of 2 GB/s for every PCle lane, enabling these SSDs to transfer data faster. ATP's PCle Gen 4 SSDs use x4 lanes for a maximum bandwidth of 8 GB/s.

Top-class performance makes these SSDs suitable for both read/write-intensive, mission-critical applications such as data logging, surveillance, and imaging systems.



Please refer to page 37 for product specifications.

#### PCIe® Gen 4 NVMe M.2 2280 SSD

#### **PRODUCT HIGHLIGHTS**

- Capacities
  - 240 GB to 3.84 TB
- Operating Temp
  - I-Temp (-40°C to 85°C): N600Si
  - C-Temp (0°C to 70°C): N600Sc
- Thermal Management for Optimal Heat Dissipation
  - Nickel-coated copper heat spreader on controller
  - · 4 mm or 8 mm fin-type heatsink design
- Security
  - AES 256-bit encryption
  - TCG Opal 2.0
- Data Integrity
  - End-to-End data path protection
- Performance
  - Read/Write up to: 6,450/6,000 MB/s





#### PCle® Gen4 NVMe U.2 SSD

#### **PRODUCT HIGHLIGHTS**

- Capacities
  - 960 GB to 7.68 TB
- Operating Temp
  - I-Temp (-40°C to 85°C): N600Si
  - C-Temp (0°C to 70°C): N600Sc
- Thermal Management for Optimal Heat Dissipation
  - 15 mm fin-type heatsink design
- Security
  - AES 256-bit encryption
  - TCG Opal 2.0
- Data Integrity
  - End-to-End data path protection
- Performance
  - Read/Write up to: 3,900/3,800 MB/s
- Hot-swappable





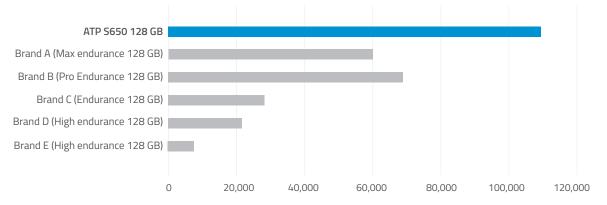
The S750/S650 Series SD and microSD memory cards built with 3D triple level cell (TLC) are made for the rigors of non-stop video recording. They meet the high endurance, low latency, and built-to-last data storage requirements of dashcams and digital video recorders (DVRs), as well as surveillance systems, autonomous vehicles, and other write-intensive applications.

The S650 Series can record Full HD videos continuously up to 109,401 hours — far longer than similar cards marketed as "high endurance." The S650 Series is based on 5K program/erase (P/E) cycles, which translate to 1.6X higher endurance than typical memory cards with 3K P/E cycles. The S750 Series, configured as pseudo single-level cell (pSLC) is based on 60K P/E cycles, while typical pSLC memory cards are rated for around 20K to 30K P/E cycles.

#### PRODUCT HIGHLIGHTS

- Capacities
  - S750 Series: 8 GB to 32 GB (SD); 8 GB to 64 GB (microSD)
  - S650 Series: 32 GB to 128 GB (SD); 32 GB to 256 GB (microSD)
- Operating Temp
  - I-Temp (-40 to 85°C): S750Pi, S650Si
  - C-Temp (-25 to 85°C): S750Sc, S650Sc
- Endurance
  - S750 Series: Up to 1,745 TB (SD); Up to 3,490 TB (microSD)
  - S650 Series: Up to 582 TB (SD); Up to 1,164 TB (microSD)
- ATP own-developed firmware
  - Read Retry, Auto Read Calibration
  - Read Disturb Protection
  - Back-up Mechanism and Sudden Power Off Recovery

- ATP own-developed advanced card analysis for System-in-Package (SiP) design
  - ATP-Developed Hardware Design Substrate with reserved testing pin is available for future component analysis.
  - Solder Mask Removal by Laser Precise and efficient method to remove solder mask so as to reach the reserved testing pins on the substrate.
  - ATP's Own Customized Debug Tool This is connected to the Hardware reserved testing pin and then linked to the Software analysis system.



High Endurance Maximum Recording Hours: ATP S650 vs. Other High-Endurance Cards

#### Notes:

Tested using 128 GB ATP S650 TLC card based on 13 Mbps (lowest bitrate of HD recording) in best-case/ideal scenario, with no other influencing factors. Information sourced by ATP from publicly available data. To record new data, the oldest data will be overwritten when the card is full. 1Mbps=1,000,000 bps



Manufactured using a new die package, the new-generation 3D TLC SATA and NVMe embedded SSDs are breaking endurance records.

The SATA A750 and A650 Series are available in M.2 2280/2242, 2.5" and mSATA form factors, while the N750 and N650 Series support the NVMe 1.3 protocol with PCIe Gen 3 x4 interface and are available as M.2 2280 modules.

Endurance enhancements compared with other SSDs:

- Near-MLC in native TLC mode: A650Si/Sc and N650Si/Sc 66% higher
- Near-SLC in pSLC: A750Pi Series 50% higher
   N750Pi Series 54% higher

Depending on drive capacity, N750Pi Series SSDs deliver maximum sustained sequential write performance of over 2000 MB/s, enabling them to run dependably for extended periods of time. This makes them highly suitable for write-intensive industrial/embedded applications that require reliable, uninterrupted operation.

N750Pi SSDs are configured entirely in pSLC mode, resulting in capacities lower than typical TLC drives but delivering higher reliability and longer service life.

#### ATP A750Pi Pseudo SLC Drives Yield 50 % Higher Endurance

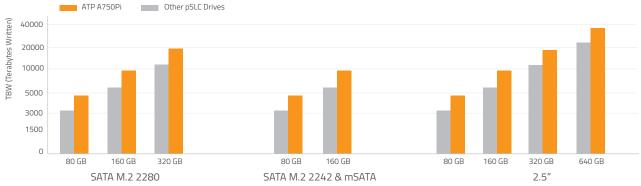


Figure 1. Comparison between ATP A750Pi and other 3D TLC drives in pseudo SLC (pSLC) mode. Endurance is expressed in terabytes written (TBW) in Sequential Write.

#### ATP A650Si/Sc 3D TLC Drives Yield 66% Higher Endurance

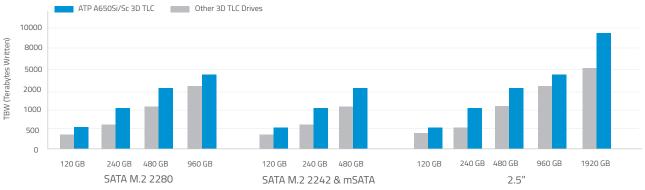


Figure 2. Comparison between ATP A650Si/Sc and other 3D TLC drives. Endurance is expressed in terabytes written (TBW) in Sequential Write.



Using a new die package, the E750Pi/Pc and E650Si/Sc Series offer long-life performance, optimized power consumption and customizable configuration options.

The E750Pi/Pc Series e.MMC offerings are built with 3D TLC NAND flash but are configured as pseudo SLC (pSLC) to offer endurance on par with SLC NAND, while E650Si/Sc Series in native TLC exceeds MLC endurance.

The E750Pi and E650Si Series are industrial temperature-operable (-40°C to 85°C), making them ideal for deployment in scenarios with extreme thermal challenges and harsh environments, while E750Pc and E650Sc support -25°C to 85°C operating temperatures for applications with non-critical thermal requirements.

#### **PRODUCT HIGHLIGHTS**

- Capacities
  - E750 Series: 10 GB to 21 GB
  - E650 Series: 32 GB to 64 GB
- Operating Temp
  - I-Temp (-40 to 85°C): E750Pi, E650Si
  - C-Temp (-25 to 85°C): E750Pc, E650Sc
- Endurance
  - E750 Series: Up to 1,034 TB
  - E650 Series: Up to 70 TB

- Shock/Vibration Proof
- Data Integrity Features:
  - Auto Refresh Technology
  - Dynamic Data Refresh Technology
  - SRAM Soft Error Detector and Recovery
  - Low-Density Parity-Check Error Correcting Code (LDPC ECC)
- Customizable Configuration (By project request)
  - 9 x 10 mm packaging option, for up to 40% space savings

## SecurStor microSD Cards Safeguard Data with Secure Boot, HW AES-256 XTS Encryption, and Customizable Security Feature

As part of the ATP SecurStor product suite, the microSD cards come with integrated features that safeguard data-at-rest as well as a wide range of optional custom features tailored to an application's individual requirements.

They are well suited for the Internet of Things (IoT), education, automotive, defense, aerospace, and other applications requiring confidentiality and reliability.

As a customization option on a per-project basis, these cards may be specially built to comply with specific sanitization standards, such as the US Air Force System Security Instruction (AFSSI) 5020.

Please refer to page 51 for product specifications.

## ATP SecurStor

#### PRODUCT HIGHLIGHTS\*

- Multi-Layer Authentication: Privilege control for up to 10 users offer high levels of protection.
- **SecurBoot:** Ensures the integrity and validity of the system's stored BIOS configuration.
- Hardware AES-256 XTS Encryption (SecurEncrypt): Protects the User Data area with the highest level of hardware encryption without performance trade-off.
- Secure Erase: Deletes the encryption key to prevent unauthorized retrieval or recovery of the user data. Compliance with US Air Force System Security Instruction (AFSSI) 5020 standard or alike is available on a per-request basis

#### PLATFORM/OS SUPPORT\*\*

- x86 Windows 10 & Linux
- ARM Raspbian Linux





#### **Customization Options**

ATP is fully capable of customizing security policies, as well as hardware, firmware, and software. For special requests, please contact the ATP sales representative in your area.

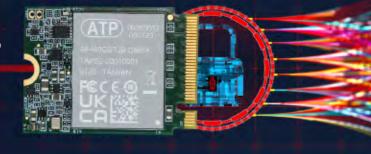
- Actual availability of specific features may vary by product and capacity.
   Please contact ATP for details.
- \*\* Support for other operating systems may be available on request.

## N700 and N600 Series: High-Endurance M.2 2230, Type 1620 HSBGA SSDs Packed with Customizable Security Features

The N700 and N600 Series accommodate a heatsink ball-grid array (HSBGA) on the M.2 2230 form factor as well as M.2 Type 1620 HSBGA SSDs with the same firmware and NAND configuration for customers who prefer a soldered-down, vibration-proof solution.

They offer hardware-based security features, such as Write Protection and Quick Erase, by project and customer request.

Please refer to page 38, 54 for product specifications.



#### PRODUCT HIGHLIGHTS

- Form factors:
  - NVMe 1.3 PCle Gen3x4 HSBGA on M.2 2230 module
  - NVMe 1.3 PCle Gen3x4 HSBGA M.2 Type 1620 (soldered down)
- Capacities
  - N700 Series (pSLC): 40 GB to 160 GB
  - N600 Series (native TLC): 120 GB to 480 GB
- Maximum Endurance
  - N700 Series: 4,280 TB
  - N600 Series: 768 TB
- Sustainable performance with ATP Optimized Thermal Throttling firmware (FW)

- Low power consumption at just 5 mW under Power State 4 (Sleep Mode)
- Host Memory Buffer (HMB) support
- Operating Temperature
  - I-Temp (-40 to 85°C)
  - C-Temp (0 to 70°C)
- Customizable Security Options (by request and project support)
  - HW Write Protect
  - HW Erase
  - \* Quick Erase
  - \* Secure Erase (AFSSI-5020)
  - AES-256 Encryption
  - TCG Opal 2.0

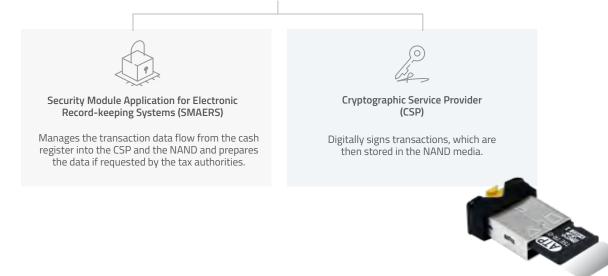
ATP Electronics Technical Security Solutions (TSE) provide you with up to 8 years of secure, tamper-proof transaction storage following the TR-03153 guidelines of Bundesamt für Sicherheit in der Informationstechnik, BSI.

A TSE is an add-on to your current POS system that ensures tamper-proof recording of all fiscal transactions to prevent unauthorized manipulation for the purpose of tax fraud. ATP's solution consists of two basic elements:

#### **PRODUCT HIGHLIGHTS**

- TSE Requirements: Compliant with the requirements of the BSI TR-03153, Common Criteria PP-SMAERS, PP-CSP
- Projected Certificate Validity: Up to 8 years (also available with 5-year validity)
- Form Factors: microSD, SD, USB
- Capacities: 8 GB and 16 GB
- Data Retention: Up to 10 years (depending on test conditions)
- Lifetime: More than 20 million signatures\*
- Signature time less than 150 ms
- OS Support: Windows, Android, Linux

#### ATP TSE Flash Solutions



<sup>\*</sup>May vary depending on payload size(s).

## High-Speed Type B CFexpress Cards: PCle 4.0 x2 Interface Delivers Next-Generation Performance

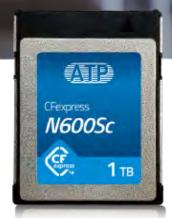
ATP CFexpress Type B memory cards utilize the PCIe 4.0 x2 interface, they deliver superior, high-speed performance compared with other cards using the PCIe 3.0 x2 interface. They are built with 3D TLC flash and offer big storage for IPC/embedded, automation, networking, test and measurement, and transportation systems as well as other applications that require excellent reliability, endurance, and performance.

The DRAM-less CFexpress card features Host Memory Buffer (HMB) support to improve random read performance, TCG-Opal and hardware write-protect security, and RAID 0, 1 compatibility. These features make them suitable storage media for entry-level data logging, high-end digital video cameras, and high-end digital and mirrorless cameras.

Please refer to page 49 for product specifications.

#### PRODUCT HIGHLIGHTS

- Capacities: 128 GB to 1 TB
- Operating Temp
- I-Temp (-40°C to 85°C): N600Si
- C-Temp (0°C to 70°C): N600Sc
- Endurance : Up to 1,000 TB
- Host Memory Buffer (HMB) support
- Security
- TCG Opal 2.0
- HW write protect (optional)
- RAID 0, 1 compatibility



## ATP NANODURA Dual UFDs Comply with USB 3.2 Gen 1 Standard to Offer "SuperSpeed" Data Transfers

Effortlessly store, share, and access files with ATP's new NANODURA Dual B600Sc Series universal flash drives (UFDs). Compliant with the Superspeed USB 3.2 Gen 1 specifications, these removable storage media can transfer data at speeds up to 5 Gb/s – a huge leap from USB 2.0 transfer speed of 480 Mb/s.

They come in capacities of 32/64/128 GB and are fitted with Type C connectors, which support reversible plug orientation.

Please refer to page 44 for product specifications.

#### PRODUCT HIGHLIGHTS

- Form Factor: USB flash drive (USB 3.2)
- Connector Type: Type C, supports reversible plug orientation
- Capacities
- 32 GB to 128 GB
- Operating Temp
- C-Temp (0 to 70°C)
- Endurance
  - Up to 84 TB
- True Plug and Play connection, supports hot swap function
- Advanced NAND management technology, global wear leveling algorithm





The N600Vc/A600Vc Series SSDs are built with triple-level cell (TLC) NAND on leading 100+ layer 3D architecture. They are targeted for industrial/embedded applications requiring reliable performance, a wide range of capacity options, and long-term supply commitment at friendly price points.

The N600Vc Series is available in M.2 2242/2280 form factors and support the NVMe 1.3 protocol with PCle Gen 3 x4 interface. The A600Vc Series is available in 2.5", M.2 2242/2280, and mSATA form factors and supports the Serial ATA (SATA) protocol and interface.

The Value Line is tailored for read-intensive applications, such as web server, box pc, kiosk/point-of-sale systems (POS), and other industrial/embedded boot drive requiring speed and reliability.

These SSDs offer lower cost per GB with a wide range of capacity offerings. They are DRAM-less, making them ideally suited for heavy random-read applications such as booting, which require minimal or even no write operations.

#### PRODUCT HIGHLIGHTS

- Capacities
  - N600Vc Series: 120 GB to 960 GB (M.2 2242/2280)
  - A600Vc Series: 32 GB to 1 TB (M.2 2242/2280, 2.5", mSATA)
- Operating Temp
  - C-Temp (0 to 70°C)

- Endurance
  - N600Vc Series: Up to 1,520 TB
  - A600Vc Series: Up to 1,530 TB
- Host Memory Buffer (HMB) support
- Firmware-based power-loss mechanism for data-at-rest protection

### ATP's DDR5 Memory Feeds the Need for Speed, Higher Density, and Lower Power



Please refer to page 30 for product specifications.

ATP introduces DDR5, the next-generation DRAM specification memory that brings several significant improvements and advantages over its previous memory generation, DDR4. Here are some of the reasons why ATP's DDR5 delivers key performance gains.

#### 2X the Speed



ATP DDR5 DIMMs debut with 4800/5600 MT/s memory bandwidth, which supersede DDR4's maximum speed of 3200 MT/s. DDR5 is expected to scale up to 6400 MT/s channel speed, thus doubling DDR4's and translating to overall higher performance.

#### Up to 256 Gb Density with 8-Layer TSV



While DDR4 maxed out at 16 Gb in a single die package (SDP), a single DDR5 DRAM die package has up to 32 Gb, allowing a maximum of 256 Gb on an 8-layer through-silicon via (TSV) package.

#### **Lower Power Consumption**



From DDR4's 1.2V, DDR5 operating voltage is a mere 1.1V, resulting in lower power consumption and more energy savings.

## (<del>/</del>)

#### **Better Power Architecture with PMIC**

DDR5 features a new power architecture that moves power management from the motherboard to the DIMM. An on-board Power Management Integrated Circuit (PMIC) regulates power for better distribution and signal integrity while reducing noise.

#### **Precise Temperature Control**



Targeted for DDR5 Registered DIMMs (RDIMMs), a temperature sensor on the DIMM provides accurate and real-time temperature monitoring and control.

#### Other Key Enhancements Over DDR4

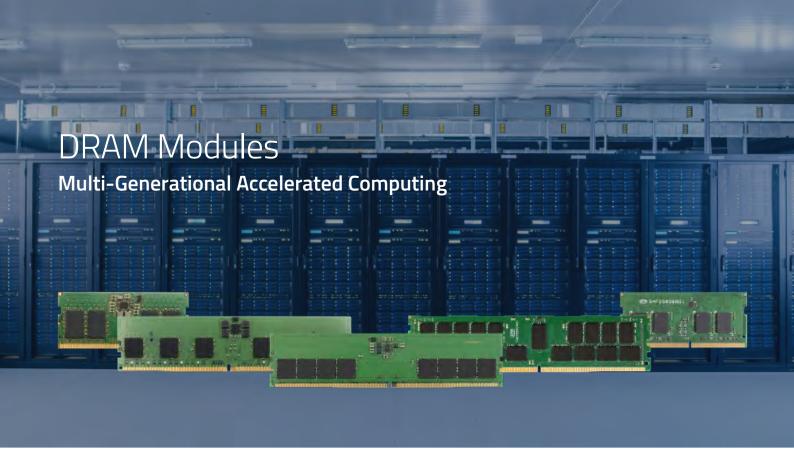
- On-Die ECC detects and corrects errors before data is sent to the CPU.
- Dual Subchannels on a DIMM. Two 40-bit-wide channels (32 data bits and 8 ECC bits) improve memory access.
- Burst length of 16. Having twice the burst length of DDR4, DDR5 can access 64 Bytes of data with a single burst and using just one of two independent channels (half a DIMM), translating to better efficiency.
- Dual Data Rate (DDR) on command and address interface, as opposed to Single Data Rate (SDR) on command and address interface with DDR4, have freed up additional pins for isolation enhancements.

## DRAM Solutions

Intense Performance for Intense Workloads

ATP's industrial DRAM modules are built tough and can meet the exacting demands of the growing enterprise. On call 24/7, these hardworking modules are fast, can withstand harsh operating environments, and can handle large bandwidth requirements. ATP's DRAM lineup consists of legacy SDRAM, and a complete range of DDR1, DDR2, DDR3, DDR4, and DDR5 modules. They are available as RDIMM, RDIMM VLP, UDIMM/UDIMM ECC, SO-DIMM/SO-DIMM ECC, Mini-RDIMM, and Mini-UDIMM/Mini-UDIMM ECC.





ATP DRAM modules meet the growing need for accelerated performance in memory-intensive and high-performance computing applications to keep up with intensifying data processing requirements as the Internet of Things (IoT) and industrial IoT (IIoT) inevitably become more pervasive. Multi-generational solutions range from legacy DDR3/DDR2/DDR1 to the latest DDR4-3200 modules and DDR5 solutions, which deliver robust performance, durable build and the right density for the toughest workloads.

#### **Key Differentiators\***

- Value-Added Customization Services
  - Conformal Coating. ATP's conformal coating solution uses parylene coating technology via chemical vapor deposition (CVD), which is compliant with US Military Material MIL-I-46058C and Fire Safety UL94V-0 Certification standards. The coating completely penetrates spaces as narrow as 0.01 mm, making it totally pinhole-free and truly conformal to shield the DRAM module from dust, chemicals, moisture, and other harmful substances.
  - Chamfering PCB Design. Chamfering refers to the process of "beveling or tapering" the connector edges for easier insertion into the memory slots. The bevel is done at specific angles, typically at around 40° to 50°.
- Wide Temperature. Wide-temperature ICs supporting -40°C to 85°C operating range offer the best solution to reach industrial grade performance at a lower cost.
- **Product Longevity Program.** Micron Technology, Inc. endorses ATP as a partner to support selected SDR/DDR/DDR2 modules. ATP will continue to manufacture legacy SDR/DDR/DDR2 DRAM modules for Micron's customers that are unable to migrate, including selected legacy DRAM modules specifically for customers using AMD Embedded/Geode platforms.
- System-Level TDBI. Test During Burn-In (TDBI) combines temperature, load, speed and time to stress test memory modules and expose weak modules. Even just 0.01% error on a 99.99% effective device can increase the failure rates at the module level and lead to failure in actual usage. ATP's system-level TDBI can detect and screen out the 0.01% error to ensure utmost reliability.

<sup>\*</sup> May vary by product and project support.

#### ATP DRAM Modules: Tested Rigorously for Maximum Reliability

Dynamic Random Access Memory (DRAM) modules perform critical tasks for rigid workloads. Many of them are installed in systems that work non-stop in high-stress environments. They are constantly exposed to thermal, environmental as well as electro-mechanical challenges. Knowing that any vulnerability that can cause unstable system operation can also drastically impact business operations, ATP goes through extra lengths to make sure that its DRAM modules are extremely reliable.

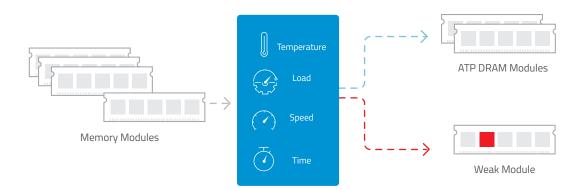
#### **Automatic Test Equipment (ATE)**

The ATE detects component defects and structural defects related to the DIMM assembly and screens out marginal timing and signal integrity (SI) sensitivities. ATE provides electrical testing patterns with various parameter settings, such as marginal voltage, signal frequency, clock, command timing and data timing under continuous thermal cycle.



#### Test During Burn-in (TDBI)

- TDBI at mass production level detects early life failures (ELF) and effectively screens out weak ICs that could fail during the early product life. It combines temperature, load, speed and time to stress test memory modules and expose the weak module.
- Even just 0.01% error on a 99.99% effective device can increase the failure rates at module level and lead to failure in actual usage.
- ATP TDBI can detect and screen out the 0.01% error to ensure utmost reliability.

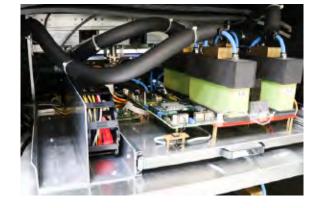


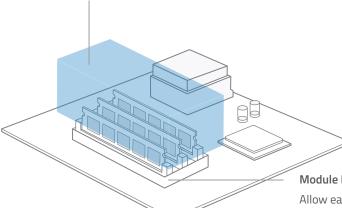
#### ATP TDBI: What Makes It Unique?

The ATP TDBI system applies extreme high/low temperature, high-low voltage, and pattern testing on DRAM modules. The system consists of:

#### The Mini Chamber

Isolates temperature cycling only to modules being tested so as not to thermally stress the rest of testing systems. This minimizes the failure of other testing components, such as the motherboards. It also allows faster debug for defects per million (DPM) fallout and reduced false failures. In conventional large thermal chambers, the failures of non-DRAM-related testing components are constant, given that the whole system is thermally stressed.



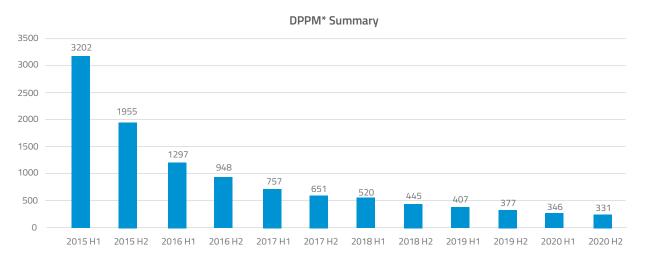


Module Riser Adapters from the Motherboard

Allow easy module insertions in production-level volumes.

#### Improvements After TDBI Adoption

The following graph shows that with ATP TDBI, the error rates decrease over time. The acceptable industry limit is 3,500 DPPM,\* but with ATP TDBI, the error rate has gone down significantly over the years.



<sup>\*</sup>DPPM = Defective Parts per Million

## DDR5: Built to Meet Ever-Growing Memory Needs with 2X the Speed, 4X the Capacity and Greater Power Efficiency



Up to

**6.4** Gbps

4800 to 6400 MHz

Memory Bandwidth

Frequency / Transfer Rate

Per die

Up to **64** Gb

Memory Density

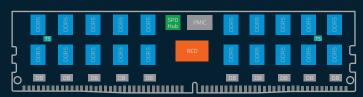
**Operating Voltage** 

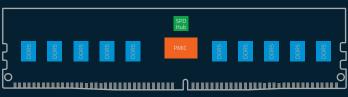
ATP's DDR5 solutions are expected to deliver performance and reliability improvements over the previous generation, especially for critical computing applications.

As the next-generation DRAM specification, DDR5 is poised to exceed DDR4 in every way. DDR5 promises faster performance, higher memory bandwidth, higher densities, and a new power management structure that delivers better power efficiency.

All of these advantages, and more, are expected to meet the ever-growing memory needs of present and future applications. Both DDR4 and DDR5 dual-inline memory modules (DIMMs) still have 288 pins, but with DDR5's higher bandwidth, this means it can transmit data faster. While the pin count is the same, DDR5 DIMMs will not fit in DDR4 sockets as the alignment key is located differently and the pinouts have been changed to accommodate the new features.

For more information on DDR5 and its advantages over DDR4, please go to page 25.





UDIMM **RDIMM** 

DDR5									
DIMM Type	RDIMM	ECC UDIMM	Non-ECC UDIMM	ECC SO-DIMM	Non-ECC SO-DIMM				
Density	16 GB to 64 GB	16 GB to 32 GB	8 GB to 32 GB	16 GB to 32 GB	8 GB to 32 GB				
Speed up to (MT/s)	4800/5600	4800/5600	4800/5600	4800/5600	4800/5600				
PCB Height*	Low profile / VLP*	Low profile / VLP*	Low profile	Low profile	Low profile				
Operating Temperature		0°C to 85°C /	-/₁Ი°C to 85°C						

\* VLP: 0.74"

### I-Temp Registered Clock Driver on Wide-Temp DDR4 RDIMMs Ensures Maximum Reliability in Extreme Temperatures



DRAM modules are typically installed in systems that operate in harsh environments and extreme temperatures that fluctuate during daytime and the nighttime, as well as in varying weather conditions; thus, memory with a broader range of temperature capabilities is becoming more necessary as most edge computing applications run 24/7, often in challenging environments.

ATP offers DDR4 wide-temp RDIMMs with industrial-temperature-rated registered clock driver (RCD) to ensure better endurance and redundancy in critical environments where commercial-grade DRAMs do not suffice.

The RCD's main function is to first receive the instructions or commands from the central processing unit (CPU) before sending them to the memory modules. This buffering reduces the strain on the CPU's memory controller, helps reduce impact on signal integrity, and maintains the same memory speed even in heavy workloads.

The following table provides a comparison between commercial grade and wide temperature RDIMMs with I-Temp RCD, which offer stability and reliability even in sub-zero temperatures.

	Commercial Grade RDIMM	Wide Temperature RDIMM
DRAM IC	Major IC	Wide-Temp IC1 (-40°C to 85°C)
RCD IC Temp Rating	Commercial Grade (0°C to 85°C)	Wide-Temp IC1 (-40°C to 85°C)
Module Operating Temp	0°C to 85°C	Industrial Grade (-40°C to 85°C)
Testing Features	ATE <sup>2</sup> & TDBI <sup>3</sup> Module-Level Test (room temp.)	ATE <sup>2</sup> & TDBI <sup>3</sup> 100% Module-Level Test (-40°C to 85°C)

<sup>1</sup> Wide-temperature ICs are ATP's best solution to reaching industrial-grade performance at lower cost through enhanced and more rigorous testing.

<sup>2</sup> ATE: Automatic Test Equipment

<sup>3</sup> TDBI: Test During Burn-in

### ATP Reaffirms Commitment to Long-Term Supply of Legacy DRAM Modules

#### ATP Meets Continued Demand for DDR3 Modules

With DDR4 as the current mainstream memory and companies preparing for DDR5, major memory makers are slowing down the production of DDR3 or phasing it out. However, systems that have been running for a long time supporting DDR3 remain widely in use for industrial, networking, and other embedded applications. Through its partnership with key suppliers, ATP is committed to supporting the continued demand for DDR3 SO-DIMM and UDIMM in the next 3 to 5 years.

#### **Product Information**

Module Type	DDR3 SO-DIMM	DDR3 UDIMM
Capacity	4 GB / 8 GB	4GB/8GB
Function	ECC/NON-ECC	ECC/NON-ECC
Frequency	1866 MHz	1866 MHz

#### Micron-ATP Partnership and License Agreements: DDR2 Continuity Program

With DDR2 still widely deployed in the US, Japan and Europe, ATP and Micron are making sure that these markets will have a steady supply of Micron DDR2 SO-DIMMs and UDIMMs for industrial/embedded systems installed in high-reliability and mission-critical environments. All modules are manufactured, tested and validated by ATP, according to the equivalent specifications and testing/validation processes of the respective Micron part number.

"Micron is dedicated to maximizing customers' infrastructure investments by ensuring prolonged support for legacy systems and applications. Our proven partnership with ATP gives our customers the benefit of receiving similar Micron products and services to support their current platforms while ATP ensures the stability of their operations well into the future."





#### Legacy (SDR/DDR) DRAM Modules

The license agreement stipulates the following conditions for ATP:

- 100% follow Micron's design. Offer extended support for these legacy products to minimize the customer's (re)qualification efforts.
- 100% follow Micron's BOM selection. Implement the same specifications for key components (such as IC configuration and Register/PLL type), as well as passive components (such as resistors, capacitors and EEPROM) to meet the specifications of Micron's BOM.
- 100% follow Micron's firmware settings. Implement SPD in addition to the manufacturer's information.
- 100% follow Micron's specifications. Each module will be manufactured to the equivalent specifications and test processes of the corresponding Micron part number.

#### **Product Information**

Module Type	Capacity	Function	Frequency	Number of Pins	PCB Height
DDR SO-DIMM	128 MB / 256 MB / 512 MB / 1 GB	Unbuffered Non-ECC	400 MHz	200	1.25"
DDR SO-DIMM (Industrial Grade)	256 MB / 512 MB	Unbuffered Non-ECC	400 MHz	200	1.25"

Build To Order (BTO)								
Module Type	Capacity	Function	Frequency	Number of Pins	PCB Height			
DDR UDIMM	256 MB / 512 MB	Unbuffered Non ECC	400 MHz	184	1.25"			
SDRAM SO-DIMM	64 MB / 128 MB / 256 MB	Unbuffered Non ECC	133 MHz	144	1.0" / 1.25"			

## Complete DRAM Portfolio

Product	DIMM Type	Capacity	Speed (MT/s, up to)	VLP/ULP*	30µ" Golden Finger	ATP TDBI	Wide Temperature	Anti-Sulfur Resistors	Conformal Coating	PCB Chamfer
	RDIMM	16 GB to 64 GB	4800/5600	•	•	•	<b>A</b>	<b>A</b>	-	<b>A</b>
	ECC UDIMM	16 GB to 32 GB	4800/5600	•	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
DDR5	Non-ECC UDIMM	8 GB to 32 GB	4800/5600	-	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
DDR4	ECC SO-DIMM	16 GB to 32 GB	4800/5600	-	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
	Non-ECC SO-DIMM	8 GB to 32 GB	4800/5600	-	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
	RDIMM	4 GB to 128 GB	3200	•	•	•	<b>A</b>	<b>A</b>	-	<b>A</b>
	ECC UDIMM	4 GB to 32 GB	3200	•	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
555	Non-ECC UDIMM	4 GB to 32 GB	3200	•	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
DDR4	ECC SO-DIMM	4 GB to 32 GB	3200	-	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
	Non-ECC SO-DIMM	4 GB to 32 GB	3200	-	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
	Mini-RDIMM	4 GB to 16 GB	2400	•	•	•	<b>A</b>	<b>A</b>	-	-
	Mini-UDIMM	4 GB to 16 GB	2400	•	•	•	<b>A</b>	<b>A</b>	-	-
	RDIMM	1 GB to 32 GB	1866	•	•	•	<b>A</b>	<b>A</b>	-	<b>A</b>
	ECC UDIMM	1 GB to 16 GB	1866	•	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
	Non-ECC UDIMM	1 GB to 16 GB	1866	•	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
DDR3	ECC SO-DIMM	1 GB to 16 GB	1866	-	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
	Non-ECC SO-DIMM	1 GB to 16 GB	1866	-	•	•	<b>A</b>	<b>A</b>	<b>A</b>	<b>A</b>
	Mini-RDIMM	1 GB to 8 GB	1600	•	•	•	<b>A</b>	<b>A</b>	-	-
	Mini-UDIMM	1 GB to 8 GB	1600	•	•	•	<b>A</b>	<b>A</b>	-	-
	ECC UDIMM	1 GB to 2 GB	800	-	•	•	<b>A</b>	-	-	-
DDR2	Non-ECC UDIMM	1 GB to 2 GB	800	-	•	•	<b>A</b>	-	-	-
	Non-ECC SO-DIMM	256 MB / 1 GB to 4 GB	800	-	•	•	<b>A</b>	-	-	-
DDR1	Non-ECC UDIMM	256 MB	400	-	•	•	-	-	-	-
ואטט	Non-ECC SO-DIMM	128 MB to 512 MB / 1 GB	400	-	•	•	<b>A</b>	-	-	-
SDRAM	Non-ECC SO-DIMM	64 MB to 256 MB	PC 133	-	•	•	-	-	-	-

<sup>▲:</sup> Optional

<sup>\*</sup> VLP: height = 0.74"

ULP: height below 0.74"

## Flash Solutions

### Specialized Storage Solutions for Mission-Critical Applications

ATP's industrial flash products deliver dependable performance, efficient responsiveness, and long usage life to accomplish mission-critical tasks. Customizable\* to customers' configurations, they come in different form factors, such as U.2, 2.5" SSDs, M.2 embedded modules, mSATA, CFexpress, CFast, CompactFlash, SD/microSD memory cards, and USB drives for enterprise and industrial applications.

They support high-speed interfaces such as SATA 6 Gb/s and the latest NVMe™ protocol on PCle® interface for reliable, blazing-fast, and future-ready performance. Managed NAND offerings include the automotive/industrial grade e.MMC and NVMe HSBGA SSD, which integrate flash memory and controller into a single package.

\* By project support.



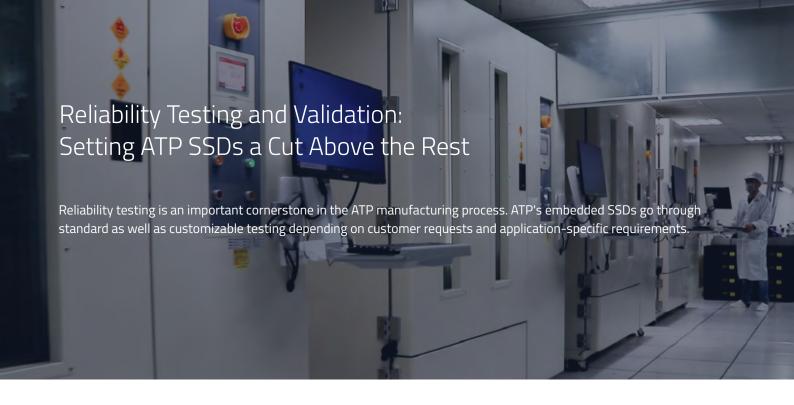


ATP flash storage products are built for different workloads, usage scenarios, operating environments and platforms. Hard-wired for sustained operation in wide temperatures (-40 °C to 85 °C) and other environmental challenges, they may also be customized according to customers' requirements. They undergo stringent reliability testing to ensure reliable performance even at extreme temperatures and voltages at sudden power off and unstable power supply. Four-Corner, Temperature Cycling, and Power Cycling are just some of the reliability tests performed to guarantee that ATP SSDs deliver outstanding performance, rugged durability, and many years of reliable performance. They support the latest high-speed NVMe™ protocol on a PCle®Gen4 x4 interface as well as proven interfaces such as SATA 6 Gb/s and USB. Various form factors include U.2, 2.5″ SSDs, M.2, mSATA and eUSB modules.

#### **Key Differentiators\***

- MLC/SLC-Level Endurance for 3D TLC Flash. ATP's latest-generation industrial/embedded SSDs built on 3D TLC NAND flash deliver exceptional endurance. SSDs in native TLC match MLC endurance, while those configured in pSLC mode are nearly on par with SLC drives.
- Thermal Management Solutions. Available for NVMe SSDs, customizable solutions combine firmware and hardware technologies to overcome overheating challenges in high-speed and high-performance storage. By understanding the performance criteria, user application and system specifications, ATP can offer tailor-fitted solutions to deliver improve sustained performance.
- High-Performance, High-Density Storage in Compact Form Factors. ATP M.2 and mSATA modules deliver power-packed performance and massive storage capacity in lean footprints, making them ideal for space-restricted systems such as embedded/IPCs, point-of-sale (POS), and networking systems.
- MCU-Based Power Loss Protection (PLP).\* Selected NVMe and SATA SSDs feature a completely new design of the PLP array, which utilizes a new power management IC (PMIC) and new firmware-programmable MCU (microcontroller unit). Integrated into its latest PLP technology, the new MCU design allows the PLP array to perform intelligently in various temperatures, power glitches and charge states.
- End-to-End Data Path Protection. ATP industrial SSDs incorporate End-to-End Data Path Protection technology to ensure the integrity of data during transfers from the host system to the storage device and back by detecting and correcting errors on multiple transfer points.

<sup>\*</sup> May vary by product and project support.





#### Reliability Demonstration Test (RDT)

Validates the mean time between failures (MTBF) rating of the drive through actual drive-level testing instead of relying on reliability prediction systems.



#### End-of-Life Validation Test

Makes sure that ATP SSDs perform reliably and maintain data integrity over their life span (and even beyond) as required.



#### PCBA Solderability Validation

Ensures effective bonding of components on the printed circuit board assembly (PCBA) for reliable electro-mechanical connections.



## Four-Corner, Temperature Cycling, and Power Cycling Tests

Demonstrate reliable performance and stored data handling without data miscompare even under harsh conditions.

Compliance Testing. Uses the following ULINK DriveMaster Test Suites to test and validate compliance:



#### **NVMe Protocol**

**NVM Express Compliance** 



#### Regression

Power cycle tests and JEDEC Workload Client/Enterprise Compliance



#### TCG Opal 2.0 Compliance

Verifies the correct behavior of storage devices implementing one or more of the Opal family SSC Specifications. Compliance is tested according to the requirements of the "TCG Storage Opal Family Test Cases Specification Version 1.00, Revision 1.00."



#### Proprietary Firmware Customization

Specialized solutions to enhance performance and features according to customers' unique usage/application-specific needs.

# PCIe® Gen 4 NVMe M.2 2280 SSD

#### PCle® Gen 4 NVMe M.2 2280 SSD Product Line Interface PCIe G4 x4 Flash Type 3D TLC Form Factor M.2 2280-D2-M M.2 2280-D6-M -40°C to 85°C 0°C to 70°C Operating Temperature (Tcase) Hardware + Firmware Based Firmware Based **Power Loss Protection Options** Optional SED Features AES 256-bit Encryption, TCG Opal 2.0 Capacity 240 GB to 1,920 GB Performance 6,450 Sequential Read (MB/s) up to Sequential Write (MB/s) up to 6.000 Random Reads IOPS up to 1,095,000 Random Writes IOPS up to 1,251,000 Endurance and Reliability 5.700 TB Endurance (TBW)2 up to Reliability MTBF @ 25°C >2,000,000 hours Others Dimensions (mm) 80.0 x 22.0 x 3.85 80.0 x 22.0 x 3.6 Certifications CE, FCC, BSMI, UKCA, RoHS, REACH Warranty 2 years

#### **KEY FEATURES**

- Superior Read/Write performance
- MCU-based Power Loss Protection Design with Level 4 (data-in-flight) protection\*
- Self-Encrypting Drive (SED) with AES 256-bit Encryption, TCG Opal 2.0 \*
- Thermal Heatsink Solutions\*\*
- End-to-End Data Path Protection
- Anti-sulfuric resistor support\*
- \* May vary by product and project support
- \*\* Customization available on a project basis.





Technologies & Add-On Services <sup>4</sup>	<b>&amp;</b>	(b)	4	(D)	<u>Û</u> <u>U</u>		١	\$\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		8	### \\\ \\ \  \  \  \  \  \  \  \  \  \  \	VS/z	
Superior	0	0	0	0	0	0	0	0	<b>A</b>	<b>A</b>	0	<b>A</b>	<b>A</b>

- 1 Case Temperature, the composite temperature as indicated by SMART temperature attributes.
- 2 Under highest Sequential write value. May vary by density, configuration and applications.
- 3 Data subject to change.
- 4 Please refer to pages 56-58. ▲: Customization option available on a project basis.

# PCIe® Gen4 High-Capacity NVMe M.2 2280 SSD

#### PCIe® Gen4 High-Capacity NVMe M.2 2280 SSD Product Line PCIe G4 x4 Interface Flash Type 3D TLC Form Factor M.2 2280-D2-M -40°C to 85°C 0°C to 70°C Operating Temperature (Tcase)<sup>1</sup> **Power Loss Protection Options** Firmware Based **Optional SED Features** AES 256-bit Encryption, TCG Opal 2.0 Capacity 3.84TB Performance 6,400 Sequential Read (MB/s) up to Sequential Write (MB/s) up to 6,000 Random Reads IOPS up to 1,000,000 Random Writes IOPS up to 400.000 Endurance and Reliability 11 400 TB Endurance (TBW)2 up to Reliability MTBF @ 25°C >2,000,000 hours Others 80.0 x 22.0 x 3.5 (M.2 2280 Bare PCBA) Dimensions (mm) 80.0 x 24.4 x12.5 (M.2 2280 with 8mm heatsink) CE, FCC, BSMI, UKCA, RoHS, REACH Certifications Warranty 2 years

- Superior Read/Write performance
- Self-Encrypting Drive (SED) with AES 256-bit encryption, TCG Opal 2.0\*
- Thermal Heatsink Solutions\*\*
- End-to-End Data Path Protection
- Anti-sulfuric resistor support\*
- \* May vary by product and project support \*\* Customization available on a project basis.



Technologies & Add-On Services <sup>4</sup>	<b>S</b>	\$	£33	<u>Û</u> , Ţ		١	\\ \  \  \  \  \  \  \  \  \  \  \  \		8	**************************************	Y6/2	
Superior	0	0	0	0	0	0	0	<b>A</b>	<b>A</b>	0	<b>A</b>	<b>A</b>

- 1 Case Temperature, the composite temperature as indicated by SMART temperature attributes.
- 2 Under highest Sequential write value. May vary by density, configuration and applications.
- 3 Data subject to change.
- 4 Please refer to pages 56-58. A: Customization option available on a project basis.

# PCIe® Gen 3 NVMe M.2 2280 / 2242 / 2230 SSD

- MCU-based Power Loss Protection Design with Level 4 (data-in-flight) protection\*
- Self-Encrypting Drive (SED) with AES 256-bit encryption, TCG Opal 2.0 \*
- Thermal Heatsink Solutions\*\*

- End-to-End Data Path Protection
- TRIM function support
- \* May vary by product and project support \*\* Customization available on a project basis.



PCIe <sup>®</sup> Gen 3 NVMe M.2 2280 / 2242 / 2230 SSD												
Product Line	Pren											
Product Line	N750Pi	N700Pi	N700Si	N700Sc	N650Si	N650Sc	N600Si	N600Sc				
Interface			PCIe 0	33 x4								
Flash Type	3D TLC (ps	SLC mode)	3D TLC (pS	SLC mode)		3D 1	ΓLC					
Form Factor	M.2 228	0-D2-M	M.2 223	0-S4-M		M.2 228	80-D2-M					
Operating Temperature (Tcase)1	-40°C t	:o 85°C	-40°C to 85°C	0°C to 70°C	-40°C to 85°C	0°C to 70°C	-40°C to 85°C	0°C to 70°C				
Power Loss Protection Options	Hardware + Fi	rmware Based	Firmwar	e Based	Hardware	+ Firmware Base	d or Firmware Bas	ed				
Optional SED Features		Д	AES 256-bit Encryp	otion, TCG Opal 2	.0							
Capacity	40 GB to 320 GB	40 GB to 640 GB	40 GB to	160 GB	120 GB	to 960 GB	120 GB to 3	3.84 TB				
			Perfor	mance								
Sequential Read (MB/s) up to	3,1	50	2,0	00		3,4	420					
Sequential Write (MB/s) up to	2,670	2,820	1,600			3,0	050					
Random Reads IOPS up to	147,	789	135,	600	222	2,700	225,200					
Random Writes IOPS up to	114,	227	112,	000	176	5,600	179,200					
			Endurance ar	nd Reliability								
Endurance (TBW) <sup>2</sup> up to	16,000 TB	21,300 TB	4,28	O TB	4,6	40 TB	10,600	ТВ				
Reliability MTBF @ 25°C			>2,000,00	00 hours								
			Oth	ers								
Dimensions (mm)	80.0 x 22.0 x 3.5 (M.2 22 80.0 x 24.4 x 12.5 (M.2 2	80 Bare PCBA) 280 with 8 mm heatsink)	30.0 x 2	2.0 x 2.5	80.0 x 22.0 x 3.5 (M.2 2280 Bare PCBA) 80.0 x 24.4 x 12.5 (M.2 2280 with 8 mm heatsink)							
Certifications		CE, FCC, BSMI, UKC	CA, ROHS, REACH  CE, FCC, BSMI, UKCA, ROHS, and REACH are available between 120 GB to 1,920 GB; RoHS/VCCI/CE/FCC a									
Warranty	5 ye	ears	2 years									

PCIe <sup>®</sup>	Gen 3 NVMe M.2	2280 / 2242 / 223	O SSD						
Product Line									
Froduct Line	N600Vc	N600Vc	N600Vi	N600Vc					
Interface		PCIe G	i3 x4						
Flash Type		3D T	TLC						
Form Factor	M.2 2280 S2-M	M.2 2242 D5-M	M.2 2230-S4-M						
Operating Temperature (Tcase) <sup>1</sup>	0°C to	0°C to 70°C							
Power Loss Protection Options		Firmwar	e Based						
Optional SED Features		-							
Capacity	120 GB to	960 GB	120GB to 480GB						
	Performance								
Sequential Read (MB/s) up to	2,6	00	2,05	50					
Sequential Write (MB/s) up to	1,8	70	1,550						
Random Reads IOPS up to	184,	300	138,000						
Random Writes IOPS up to	145,	900	112,6	500					
		Endurance a	nd Reliability						
Endurance (TBW) <sup>2</sup> up to	1,520	O TB	768	ТВ					
Reliability MTBF @ 25°C		>2,000,00	00 hours						
		Oth	iers						
Dimensions (mm)	80.0 x 22.0 x 2.2	42.0 x 22.0 x 3.6	30.0 x 22	2.0 x 2.5					
Certifications	CE, FCC, BSMI, UKCA, RoHS, REACH								
Warranty	2 years								

Technologies & Add-On Services³		<b>&amp;</b>	(4)	\$	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	<u>1, 13</u>		٩			8	\$\frac{5}{5}\frac{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac{5}{5}\frac	<b>     </b>	VS/z		Tius"
	Premium	0	0	0	0	0	0	0	0	<b>A</b>	0	_	0	<b>A</b>	<b>A</b>	_
PCle® Gen3 NVMe M.2 2280 / 2242 / 2230	Superior	0	0	0	0	0	0	0	0	<b>A</b>	0	_	<b>A</b>	<b>A</b>	<b>A</b>	_
	Value	0	0	_	0	0	0	0	0	_	_	_	_	<b>A</b>	<b>A</b>	_
PCle <sup>®</sup> Gen3 NVMe M.2 2280 SSD ( 3.84 TB Model	Superior	0	0	_	0	0	0	0	0	<b>A</b>	<b>A</b>	0	0	_	<b>A</b>	<b>A</b>

<sup>1</sup> Case Temperature, the composite temperature as indicated by SMART temperature attributes.

<sup>2</sup> Under highest Sequential write value. May vary by density, configuration and applications.

# PCIe® Gen4 NVMe U.2 SSD

- 15 mm Fin-Type Heatsink Design
- MCU-based Power Loss Protection Design with Level 4 (data-in-flight) protection\*
- Self-Encrypting Drive (SED) with AES 256-bit Encryption, TCG Opal 2.0\*
- End-to-End Data Path Protection
- Hot-swappable
- Anti-sulfuric resistor support\*
- \* May vary by product and project support



	PCIe® Gen4 NVMe U.2 SSD	
Due doest Line	Sup	
Product Line	N600Si³	N600Sc³
Interface	PCIe	G4 x4
Flash Type	3D	TLC
Form Factor	2.	5"
Operating Temperature (Tcase) <sup>1</sup>	-40°C to 85°C	0°C to 70°C
Power Loss Protection Options	Hardware + Fi	rmware Based
Optional SED Features	AES 256-bit Encry	ption, TCG Opal 2.0
Capacity	960 GB t	o 7.68 TB
	Perfor	mance
Sequential Read (MB/s) up to	3,9	900
Sequential Write (MB/s) up to	3,8	300
Random Reads IOPS up to	670	,000,
Random Writes IOPS up to	601	,000
	Endurance a	nd Reliability
Endurance (TBW) <sup>2</sup> up to	22,80	00 TB
Reliability MTBF @ 25°C	>2,000,0	000 hours
	Oth	ners
Dimensions (mm)	100 x 69	9.85 x 15
Certifications	RoHS/VCCI/O	CE/FCC/UKCA
Warranty	2 ye	ears

Technologies & Add-On Services"	<b>€</b>	(\$)	4	₹ <u></u>			٩	\$\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		8	\$\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	VSZ		(Times
	0	0	0	0	0	0	0	0	<b>A</b>	<b>A</b>	0	<b>A</b>	<b>A</b>	<b>A</b>

- ${\tt 1\,Case\,Temperature}\, as\, indicated\, by\, {\tt SMART}\, temperature\, attributes.$
- 2 Under highest Sequential write value. May vary by density, configuration and applications.

# PCIe® Gen3 NVMe U.2 SSD

- Thermal Management Solutions\*
- High-Capacity NVMe DriveLDPC & RAID Data Recovery
- End-to-End Data Path Protection
- S.M.A.R.T / TRIM / Global Wear Leveling
- Hot-swappable
- \* Customization available on a project basis



	PCIe* Gen3 NVMe U.2 SSD
B 1 111	
Product Line	N600Si
Interface	PCIe G3 x4
Flash Type	3D TLC
Form Factor	2.5"
Operating Temperature (Tcase) <sup>1</sup>	-40°C to 85°C
Power Loss Protection Options	Hardware + Firmware Based
Optional SED Features	AES 256-bit Encryption, TCG Opal 2.0
Capacity	960 GB to 7.68 TB
	Performance
Sequential Read (MB/s) up to	3,100
Sequential Write (MB/s) up to	1,400
Random Reads IOPS up to	190,000
Random Writes IOPS up to	168,000
	Endurance and Reliability
Endurance (TBW) <sup>2</sup> up to	21,000 TB
Reliability MTBF @ 25°C	>2,000,000 hours
	Others
Dimensions (mm)	100.0 x 69.85 x 7.0
Certifications	RoHS, VCCI, CE, FCC
Warranty	2 years

Technologies & Add-On Services³	<b>&amp;</b>	(\$)	\$	£	<u> </u>		٩	\$\[ \cdot \c		8	555	**************************************		Co.
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# SATA III M.2 2280 / 2242 SSD

- MCU-based Power Loss Protection Design with Level 4 (data-in-flight) protection\*
- Self-Encrypting Drive (SED) with AES 256-bit encryption, TCG Opal 2.0\*\*
- LDPC & RAID Data Recovery
- End-to-End Data Path Protection
- TRIM / Global Wear Leveling support

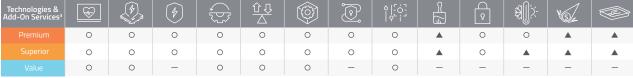
- \* May vary by product and project support
- \*\* Customization available on a project basis





SATA III M.2 2280 SSD												
Product Line												
Product Line	A750Pi	A700Pi	A650Si	A650Sc	A600Si	A600Sc	A600Vc					
Interface				SATA III 6 Gb/s								
Flash Type	3D TLC (p:	SLC mode)		3D.	TLC		3D TLC					
Form Factor				2280 D2-B-M			2280 S2-B-M					
Operating Temperature (Tcase)¹		-40°C to 85°C		0°C to 70°C	-40°C to 85°C	0°C to	70°C					
Power Loss Protection Options			Hardy	ware + Firmware Ba	ised		Firmware Based					
Optional SED Features		AES	5 256-bit Encryption	TCG Opal 2.0			-					
Capacity	80 GB to	320 GB		32 GB to 1 TB								
				Performance								
Sequential Read (MB/s) up to	56	50	56	0	56	0	560					
Sequential Write (MB/s) up to	57	20	48	0	51	525						
Random Reads IOPS up to	90,0	000	100,0	000	100,0	72,000						
Random Writes IOPS up to	88,	000	90,0	00	88,0	000	85,000					
			End	lurance and Reliabil	ity							
Endurance (TBW) <sup>2</sup> up to	19,200 TB	12,800 TB	4,655	5 TB	2,792	2 TB	1,530 TB					
Reliability MTBF @ 25°C				>2,000,000 hours								
				Others								
Dimensions (mm)				80 x 22 x 3.35			80 x 22 x 2.2					
Certifications			CE, FCC,	BSMI, UKCA, RoHS,	REACH							
Warranty	5 years 2 years											

SATA III M.2 2242 SSD												
5 1								Value				
Product Line	A800Pi	A750Pi	A700Pi	A650Si	A650Sc	A600Si	A600Sc					
Interface				SATA III 6 Gb/s								
Flash Type	SLC	3D TLC (p	SLC mode)		3D	TLC		3D TLC				
Form Factor				2242 D2-B-M								
Operating Temperature (Tcase)¹		-40°C to 85°C		-40°C to 85°C	0°C to 70°C	-40°C to 85°C	0°C to 70°C	0°C to 70°C				
Power Loss Protection Options			Hard	ware + Firmware Ba	sed			Firmware Based				
Optional SED Features	- AES 256-bit Encryption, TCG Opal 2.0							-				
Capacity	8 GB to 64 GB	40 GB to	160 GB		120 GB to	480 GB		32 GB to 1 TB				
				Performance								
Sequential Read (MB/s) up to	530	56	50	56	50	50	60	560				
Sequential Write (MB/s) up to	400	57	20	48	30	5	10	525				
Random Reads IOPS up to	76,000	68,	000	100	,000	100	,000	70,500				
Random Writes IOPS up to	76,000	88,	000	90,	000	88,	000	81,000				
			E	Endurance and Reliab	oility							
Endurance (TBW) <sup>2</sup> up to	5,333 TB	9,600 TB	6,400 TB	2,32	7 TB	1,39	6 TB	1,530 TB				
Reliability MTBF @ 25°C				>2,000,000 hours								
				Others								
Dimensions (mm)	42 x 22 x 3.5											
Certifications	CE, FCC, UKCA, RoHS, REACH											
Warranty		5 years				2 years						
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# SATA III 2.5" SSD

- MCU-based Power Loss Protection Design with Level 4 (data-in-flight) protection\*
- Self-Encrypting Drive (SED) with AES 256-bit encryption, TCG Opal 2.0\*
- NSA-compliant Secure Erase\*
- MIL-STD-810G standards\*
- \* May vary by product and project support



SATA III 2.5" SSD												
								Value				
Product Line	A800Pi	A750Pi	A700Pi	A650Si	A650Sc	A600Si	A600Sc	A600Vc				
Interface				SATA III 6 Gb/s								
Flash Type	SLC	3D TLC (p	SLC mode)		3D	TLC						
Form Factor		2	2.5"									
Operating Temperature (Tcase)¹		-40°C to 85°C		-40°C to 85°C	0°C to 70°C	-40°C to 85°C	0°C t	o 70°C				
Power Loss Protection Options			Hard	ware + Firmware Ba	sed			Firmware Based				
Optional SED Features	-		AES	256-bit Encryption,	TCG Opal 2.0			-				
Capacity	8 GB to 256 GB	80 GB t	o 640 GB		120 GB to	1,920 GB		32 GB to 1 TB				
				Performance								
Sequential Read (MB/s) up to	520	5	60		5	60		560				
Sequential Write (MB/s) up to	420	5	20		5	20		525				
Random Reads IOPS up to	76,000	90,	.000		100	,000		72,000				
Random Writes IOPS up to	74,000	88,	.000		91,	000		85,000				
			En	durance and Reliabi	lity							
Endurance (TBW) <sup>2</sup> up to	21,333 TB	38,400 TB	25,600 TB	9,310	) TB	5,58	5 TB	1,530 TB				
Reliability MTBF @ 25°C				>2,000,000 hours								
Reliability Number of Insertions	10,000 minimum											
				Others								
Dimensions (mm)	100 x 69.85 x 9.2			100 x 69.85 x 7/9.2	2			100 x 69.85 x 7				
Certifications	CE, FCC, UKCA, RoHS, REACH		CE, F	CC, BSMI, UKCA, Rol	HS, REACH							
Warranty		5 years				2 years						

Technologies & Add-On Services <sup>3</sup>	<b>S</b>	\$ P	4		$\frac{\hat{U}}{\triangle}$		\$\[\frac{1}{2}\]		P	***************************************	VS/2	
Premium	0	0	0	0	0	0	0	<b>A</b>	0	0	<b>A</b>	<b>A</b>
Superior	0	0	0	0	0	0	0	<b>A</b>	0	<b>A</b>	<b>A</b>	<b>A</b>
Value	0	0	_	0	0	0	0	_	_	_	_	_

<sup>1</sup> Case Temperature, the composite temperature as indicated by SMART temperature attributes. 2 Under highest Sequential write value. May vary by density, configuration and applications.

<sup>3</sup> Please refer to pages 56-58. **\( \Delta : Customization option available on a project basis. \)** 

# SATA III mSATA SSD

- MCU-based Power Loss Protection Design with Level 4 (data-in-flight) protection\*
- Self-Encrypting Drive (SED) with AES 256-bit encryption,
   TRIM / Global Wear Leveling support TCG Opal 2.0\*
- \* May vary by product and project support

- LDPC & RAID Data Recovery
- End-to-End Data Path Protection



				SATA III mSATA SSE				
Product Line	A800Pi	A750Pi	A700Pi	A650Si	A650Sc	A600Si	A600Sc	A600Vc
Interface				SATA III 6 Gb/s				
Flash Type	SLC	3D TLC (	pSLC mode)		3D	TLC		
Form Factor			MO-300A					
Operating Temperature (Tcase) <sup>1</sup>	-40°C to 85°C	-40°C to 85°C		-40°C to 85°C	0°C to 70°C	-40°C to 85°C	0°C to 70°C	0°C to 70°C
Power Loss Protection Options		Hardware + Firmware Based						
Optional SED Features	AES 128/256-bit Encryption		AES 256-bit Encryption, TCG Opal 2.0					
Capacity	8 GB to 128 GB	40 GB t	to 160 GB		120 GB	to 480 GB		32 GB to 1 TB
				Performance				
Sequential Read (MB/s) up to	530	Ē	560	560		56	50	560
Sequential Write (MB/s) up to	430		520	480		510		525
Random Reads IOPS up to	76,000	90,000	94,000	100,00	00	100,000		72,000
Random Writes IOPS up to	-	88,000	85,000	90,00	0	88,	000	85,000
			I	Endurance and Reliab	ility			
Endurance (TBW) <sup>2</sup> up to	10,667 TB	9,600 TB	6,400 TB	2,327	ГВ	1,39	6 TB	1,530 TB
Reliability MTBF @ 25°C				>2,000,000 hours	5			
				Others				
Dimensions (mm)				50.8 x 29.85 x 3.5				
Certifications	CE, FCC, UKCA, RoHS, REACH			CE	E, FCC, BSMI, UKCA	A, RoHS, REACH		
Warranty		5 years				2 years		

Technologies & Add-On Services	3 <u></u>	\$ P	\$						8	<b>₩</b>	VS/z	
Premium	0	0	0	0	0	0	0	<b>A</b>	0	0	<b>A</b>	<b>A</b>
Superior	0	0	0	0	0	0	0	<b>A</b>	0	<b>A</b>	<b>A</b>	<b>A</b>
Value	0	0	-	0	0	0	_	_	_	_	_	_

# **USB 3.2 NANODURA Dual**

- Superior Random Write performance
- Global wear leveling
- Bad block management algorithm
- High reliabilityPlug and Play with hot-swappable connection supported
- OTG Type-C connector supported



	USB 3.2 NANODURA Dual				
Product Line	Superior				
Product Line	B600Sc				
Interface	USB 3.2				
Flash Type	TLC				
Form Factor	USB Type-A USB Type-A/Type-C Dual Connector (Optional)				
Operating Temperature	0°C to 70°C				
Power Loss Protection Options	Firmware Based				
Optional SED Features	-				
Capacity	32 GB to 128 GB				
	Performance				
USB 3.1 Sequential Read (MB/s) up to	270				
USB 3.1 Sequential Write (MB/s) up to	85				
USB 2.0 Sequential Read (MB/s) up to	45				
USB 2.0 Sequential Write (MB/s) up to	30				
	Endurance and Reliability				
Endurance (TBW) <sup>1</sup> up to	84 TB				
Reliability MTBF @ 25°C	>2,000,000 hours				
Reliability Number of Insertions	10,000 minimum				
	Others				
Dimensions (mm)	28 x 12.25 x 4.65 Dual Connector: 36.40 x 12.25 x 4.65				
Certifications	CE, FCC, UKCA, RoHS				
Warranty	2 years				

Technologies & Add-On Services <sup>2</sup>	<b>&amp;</b>	\$	<u>Î</u>	SiP
Superior	0	0	0	0

<sup>1</sup> Under highest Sequential write value. May vary by density, configuration and applications. 2 Please refer to pages 56-58. **\( \Lambda**: Customization option available on a project basis.

# **USB 2.0 NANODURA**

	USB 2.0 NANODURA			
Product Line				
Product Line	B800Pi	B600Sc		
Interface	USB 2.0	(480 Mbps)		
Flash Type	SLC	MLC		
Form Factor	USB T	ype-A		
Operating Temperature	-40°C to 85°C	0°C to 70°C		
Power Loss Protection Options	Firmwa	ire Based		
Optional SED Features		-		
Capacity	512 MB to 8 GB	4 GB to 8 GB		
	Perfor	rmance		
Sequential Read (MB/s) up to	31	26		
Sequential Write (MB/s) up to	21	10		
	Endurance a	nd Reliability		
Endurance (TBW)1 up to	192 TB	9.6 TB		
Reliability MTBF @ 25°C	>5,000,000 hours	>2,000,000 hours		
Reliability Number of Insertions	10,000	minimum		
	Ot	hers		
Dimensions (mm)	34 x 1	2.2 x 4.5		
Certifications	CE, FCC, I	UKCA, RoHS		
Warranty	5 years	2 years		

Technologies & Add-On Services²	<b>S</b>	( <del>þ</del> )	<u>î</u>	<b>₩</b>	\$iP
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	0	0	0	_	0

# USB 2.0 eUSB

	USB 2.0	0 eUSB					
B 4 444							
Product Line	B800Pi	B800Pi	B600Sc				
Interface	C	ompatible with USB 2.0 (480 Mb	ps)				
Flash Type		SLC	MLC				
Form Factor	Pitch 2.54 mm / 2.00 mm						
Operating Temperature		-40°C to 85°C	0°C to 70°C				
Power Loss Protection Options	Firmware Based	Hardware + Fir	mware Based				
Optional SED Features		-					
Capacity	1 GB to 16 GB	1 GB to 32 GB	8 GB to 32 GB				
	Perfor	rmance					
Sequential Read (MB/s) up to	36	30	25				
Sequential Write (MB/s) up to	23	25	19				
	Endurance a	ınd Reliability					
Endurance (TBW) <sup>1</sup> up to	1,548 TB	1,280 TB	38.4 TB				
Reliability MTBF @ 25°C	>5,000,0	00 hours	>2,000,000 hours				
Reliability Number of Insertions		10,000 minimum					
	Otl	ners					
Dimensions (mm)		36.9 x 26.6 x 9.5					
Certifications		CE, FCC, UKCA, RoHS					
Warranty	5 years 2 years						

#### Technologies & Add-On Services<sup>2</sup> 0 0 0 0 0 0

# **KEY FEATURES**

- Global wear leveling
- Bad block management algorithm
- High reliability
- Plug and Play with hot-swappable connection supported



- Superior Random Write Performance
- Global wear leveling
- Power Loss Protection
- Hardware Write Protect\*
- \* May vary by product and project support





From smart factory to smart delivery, these small, low-power removable storage devices are excellent for surveillance, robotics, point-of-sale (POS) transactions, and handheld computing to swap operating systems (OS) and/or application programs or to extend storage capacity. The small yet ruggedized form factor is IP57/IP67-certified and supports the industrial temperature range (-40°C to 85°C) to assure reliable function in harsh environments.

ATP industrial SD and microSD cards offer excellent portability and expansion as removable storage media. Also available as Technical Security Solutions (TSE) for the German fiscal market, TSE microSD cards ensure tamper-proof point-of-sale (POS) transactions.

ATP offers a series of products compliant with CompactFlash Association standards, from legacy CF cards and CFast ( SATA interface ) to CFexpress ( PCle/NVMe ). ATP's latest CFexpress Type B memory cards are the most common PCle/NVMe form factors of CFA specifications using the PCle 4.0 x 2 interface. They deliver superior high-speed performance compared with other cards using the PCle 3.0 x 2 interface.

# **Key Differentiators\***

- One Size Does Not Fit All. Applications for removable storage are so numerous and so varied that off-the-shelf solutions may not be suitable for specific content volumes, security, reliability and endurance requirements. ATP can custom configure firmware and hardware so customers get what they really need.
- ATP Joint Validation Service.\*\* Compatibility and function tests are conducted using client's host devices and systems to ensure compatibility.
- Complete Coverage Rapid Diagnostic Test includes testing in extreme temperatures to ensure reliable operation from -40°C to 85°C. RDT covers all areas of the storage device including user, firmware and spare areas.
- Heavy Duty Construction. Whether manufactured using System in Package (SiP) or Surface Mount Technology (SMT), ATP memory cards are exceptionally robust, resistant to damaging elements such as dust (IP5X/IP6X), humidity/water (IPX7), electrostatic discharge (ESD), extreme temperature, shock/vibration, and more.

<sup>\*</sup> May vary by product and project support.

<sup>\*\*</sup> Value-added service

# SD/SDHC/SDXC Card

- SD Life Monitor
- High endurance
- Low latency
- Read Disturb Protector
- Power failure protectionIndustrial temperature100% MP Level Test









	SD/SDHC/SDXC Card										
Product Line	S800Pi	S750Pi	S700Pi	S750Sc	S700Sc	S650Si	S650Sc				
Interface	512 MB to 2 GB, HS mode 4 GB to 8 GB, UHS-I	UH	IS-I	UHS-I							
Flash Type	SLC	3D TLC (ps	SLC mode)	3D TLC (p	SLC mode)	3D -	ΓLC				
Form Factor		SD Card									
Operating Temperature		-40°C to 85°C		-25°C	to 85°C	-40°C to 85°C	-25°C to 85°C				
Power Loss Protection Options	Firmware Based										
Optional SED Features				-							
Capacity	512 MB to 8 GB	8 GB to 32 GB	8 GB to 64 GB	8 GB to 32 GB	8 GB to 64 GB	32 GB to	128 GB				
			Perf	ormance							
Sequential Read (MB/s) up to	68	99	95	99	95	96					
Sequential Write (MB/s) up to	39	82	70	82	70	5	7				
			Endurance	and Reliability							
Endurance (TBW)1 up to	192 TB	1,745 TB	1,164 TB	1,745 TB	1,164 TB	582	TB				
Reliability MTBF @ 25°C	>5,000,000 hours	>3,000,0	000 hours	>3,000,0	000 hours	>2,000,0	00 hours				
Reliability Number of Insertions			20,000 (SDA s	pec minimum 10,00	0)						
				Others							
Dimensions (mm)			32.0	x 24.0 x 2.1							
Certifications			CE, FCC	C, UKCA, RoHS							
Warranty		5 years		3 years	2 years	3 ує	ears				

	SD/SI	OHC/SDXC Card		
Product Line				
Product Line	S600Si	S600Sc	S600Sia/Sca	S600Sc
Interface		UH	S-I	
Flash Type	3D TLC	MLC	MLC / 3D TLC	3D TLC
Form Factor		SD (	Card	
Operating Temperature	-40°C to 85°C	-25°C to 85°C	-40°C to 85°C/ -25°C to 85°C	-25°C to 85°C
Power Loss Protection Options		Firmwar	e Based	
Optional SED Features		-	-	
Capacity	32 GB to 512 GB	8 GB to 16 GB	8 GB to 64 GB	32 GB to 512 GB
	Perf	ormance		
Sequential Read (MB/s) up to	96	68	9	96
Sequential Write (MB/s) up to	66	23	65	66
	Endurance	and Reliability		
Endurance (TBW)1 up to	1,396 TB	19 TB	307 TB	1,396 TB
Reliability MTBF @ 25°C		>2,000,0	00 hours	
Reliability Number of Insertions		20,000 (SDA spec	minimum 10,000)	
	C	thers		
Dimensions (mm)		32.0 x 2	4.0 x 2.1	
Certifications		CE, FCC, UI	KCA, RoHS	
Warranty		2 ye	ears	

Technologies & Add-On Services		\$				6   1   4   1   1   1   1   1   1   1   1		***************************************	ŠiP		(Times
Premium	<b>A</b>	0	0	0	<b>A</b>	_	0	0	0	0	<b>A</b>
Superior	<b>A</b>	0	0	0	0	<b>A</b>	0	<b>A</b>	0	0	<b>A</b>

# microSD/microSDHC/microSDXC Card

- SD Life Monitor
- High enduranceLow latency
- Read Disturb Protector
- Power failure protectionIndustrial temperature100% MP Level Test







microSD/microSDXC Card									
Product Line									
Product Line	S800Pi	S750Pi	S700Pi	S750Sc	S700Sc	S650Si	S650Sc		
Interface	512 MB to 2 GB, HS mode 4 GB to 8 GB, UHS-I			UHS-I					
Flash Type	SLC	3D TLC (pS	SLC mode)	3D TLC (p	SLC mode)	3D	TLC		
Form Factor		microSD Card							
Operating Temperature		-40°C to 85°C		-25°C	to 85°C	-40°C to 85°C	-25°C to 85°C		
Power Loss Protection Options		Firmware Based							
Optional SED Features			-						
Capacity	512 MB to 8 GB 8 GB to 64 GB			8 GB t	o 64 GB	32 GB to	256 GB		
			Performance						
Sequential Read (MB/s) up to	68	99	95	99	95	99			
Sequential Write (MB/s) up to	39	82	70	82	70	70 59			
		End	lurance and Reliabili	ty					
Endurance (TBW)1 up to	192 TB	3,490 TB	1,164 TB	3,490 TB		1,164 TB			
Reliability MTBF @ 25°C	>5,000,000 hours	>3,000,0	000 hours	>3,000,	000 hours	>2,000,0	00 hours		
Reliability Number of Insertions		20,000	(SDA spec minimum	10,000)					
			Others						
Dimensions (mm)			15.0 x 11.0 x 1.0						
Certifications		CE	, FCC, UKCA, RoHS						
Warranty		5 years		3 years	2 years	3 y	ears		

microSD	/microSDHC/micros	SDXC Card			
	Superior				
Product Line	S600Si	S600Sc	S600Sc		
Interface		UHS-I			
Flash Type	3D TLC	MLC	3D TLC		
Form Factor		microSD Card			
Operating Temperature	-40°C to 85°C	-25°C to 85°C	-25°C to 85°C		
Power Loss Protection Options		Firmware Based			
Optional SED Features		-			
Capacity	32 GB to 512 GB	8 GB to 32 GB	32 GB to 512 GB		
	Performance				
Sequential Read (MB/s) up to	96	68	96		
Sequential Write (MB/s) up to	66	24	66		
End	lurance and Reliabili	ty			
Endurance (TBW)1 up to	1,396 TB	38 TB	1,396 TB		
Reliability MTBF @ 25°C		>2,000,000 hours			
Reliability Number of Insertions	20,000 (9	SDA spec minimum	10,000)		
	Others				
Dimensions (mm)		15.0 x 11.0 x 1.0			
Certifications	С	E, FCC, UKCA, RoHS	5		
Warranty		2 years			

Technologies & Add-On Services <sup>2</sup>	<u></u>	4		<u>1, 1</u>		o   - o -		# <u></u>	SiP		(Till)
Premium	<b>A</b>	0	0	0	<b>A</b>	_	0	0	0	0	<b>A</b>
Superior	<b>A</b>	0	0	0	0	<b>A</b>	0	<b>A</b>	0	0	<b>A</b>

<sup>1</sup> Under highest Sequential write value. May vary by density, configuration and applications. 2 Please refer to pages 56-58. **\( \)**: Customization option available on a project basis.

# PCIe® Gen4 NVMe CFexpress Card

- Superior Read/Write performance
- Self-Encrypting Drive (SED) with AES 256-bit Encryption, TCG Opal 2.0\*
- DRAM-less configuration supporting Host Memory Buffer (HMB)\*
- Hardware Write Protect\*
- Anti-sulfuric resistor support\*
- \* May vary by product and project support



PCIe® Gen4 NVMe CFexpress Card								
Product Line								
Product Line	N600Si <sup>2</sup> N600Sc <sup>2</sup>							
Interface	PCIe G4 x2							
Flash Type	3D TLC							
Form Factor	CFexpress Type B							
Operating Temperature	-40°C to 85°C 0°C to 70°C							
Power Loss Protection Options	Firmware Based							
Optional SED Features	AES 256-bit Encryption, TCG Opal 2.0							
Capacity	128 GB to 1 TB							
	Performance							
Sequential Read (MB/s) up to	3,500							
Sequential Write (MB/s) up to	3,100							
Random Reads IOPS up to	210,000							
Random Writes IOPS up to	200,000							
	Endurance and Reliability							
Endurance (TBW)1 up to	1,000 TB							
Reliability MTBF @ 25°C	>2,000,000 hours							
Reliability Number of Insertions	10,000 minimum							
	Others							
Dimensions (mm)	29.6 x 38.5 x 3.8							
Certifications	CE, FCC, RoHS, UKCA							
Warranty	2 years							



<sup>1</sup> Under highest Sequential write value. May vary by density, configuration and applications.

<sup>2</sup> Data subject to change.

<sup>3</sup> Please refer to pages 56-58. ▲: Customization option available on a project basis.

# **CFast Card**

	CFast Card							
Product Line	Premium							
Product Line	A800Pi							
Interface	SATA III 6 Gb/s							
Flash Type	SLC							
Form Factor	CFast Type I							
Operating Temperature	-40°C to 85°C							
Power Loss Protection Options	Hardware + Firmware Based							
Optional SED Features	-							
Capacity	8 GB to 32 GB							
	Performance							
Sequential Read (MB/s) up to	500							
Sequential Write (MB/s) up to	300							
Random Reads IOPS up to	35,800							
Random Writes IOPS up to	-							
E	Endurance and Reliability							
Endurance (TBW)1 up to	2,667 TB							
Reliability MTBF @ 25°C	>2,000,000 hours							
Reliability Number of Insertions	10,000 minimum							
	Others							
Dimensions (mm)	36.4 x 42.8 x 3.6							
Certifications	CE, FCC, UKCA, RoHS							
Warranty	5 years							

# **KEY FEATURES**

- Advanced wear leveling algorithm
- Bad block management
- AutoRefresh technology
- Power Loss Protection
- S.M.A.R.T



Technologies & Add-On Services <sup>2</sup>	<b>&amp;</b>	\$	4		<u>1, 1</u>			<b>₩</b>	VS/2	
Premium	0	0	<b>A</b>	0	0	0	0	0	<b>A</b>	<b>A</b>

- 1 Under highest Sequential write value. May vary by density, configuration and applications.
- 2 Please refer to pages 56-58. A: Customization option available on a project basis.

# CompactFlash Card

	CompactF	lash Card			
5 1 11	Premium				
Product Line	1800Pi	1700Sc	1600Sc		
Interface	UDMA 0~4	UDN	IA 0~6		
Flash Type	SLC	Pseudo SLC	MLC		
Form Factor		CF Type I			
Operating Temperature	-40°C to 85°C	0°C t	o 70°C		
Power Loss Protection Options	Hardware + Firmware Based	Firmwa	re Based		
Optional SED Features		-			
Capacity	512 MB to 32 GB	8 GB to 16 GB	16 GB to 32 GB		
	Performance				
Sequential Read (MB/s) up to	61	110	108		
Sequential Write (MB/s) up to	55	80	46		
	Endurance a	nd Reliability			
Endurance (TBW)1 up to	1,280 TB	128 TB	38 TB		
Reliability MTBF @ 25°C	>5,000,000 hours	>2,000,	000 hours		
Reliability Number of Insertions		10,000 minimum			
	Oth	ers			
Dimensions (mm)		36.4 x 42.8 x 3.3			
Certifications		CE, FCC, RoHS, UKCA			
Warranty	5 years	2 \	years		

- Global wear leveling and bad block management
- AutoRefresh technology
- Power Loss Protection
- Power saving mode
- S.M.A.R.T support





- Technologies & Add-On Services²
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- 1 Under highest Sequential write value. May vary by density, configuration and applications.

# SecurStor microSD Card

#### **KEY FEATURES**

- Additional AES Key Protection
- Library access possible (MBR required)
- Authentication / Privilege Control
- Total 10 User Accounts can set up privileges individually

#### **SECURITY FEATURES\***

- Multi-Layer Authentication:
   Privilege control for up to 10 users offer high levels of protection.
- **SecurBoot:** Ensures the integrity and validity of the system's stored BIOS configuration.
- Hardware AES-256 XTS Encryption (SecurEncrypt):

Protects the User Data area with the highest level of hardware encryption without performance trade-off.

- Secure Erase: Deletes the encryption key to prevent unauthorized retrieval or recovery of the user data.
  - Compliance with US Air Force System Security Instruction (AFSSI) 5020 standard or alike is available on a per-request basis
- \* Actual availability of specific features may vary by product and capacity. Please contact ATP for details.

Product Name	SecurStor microSD
Product Line	SecurStor
Flash Type	MLC
Density	4 GB to 16 GB
Performance Sequential Read (MB/s) up to	10.35
Performance Sequential Write (MB/s) up to	5.3
Interface	UHS-I
Operating Temperature	-25°C to 85°C
Reliability MTBF @ 25°C	>2,000,000 hours
Reliability Number of Insertions	10,000
Dimensions (mm)	15.0 x 11.0 x 1.0





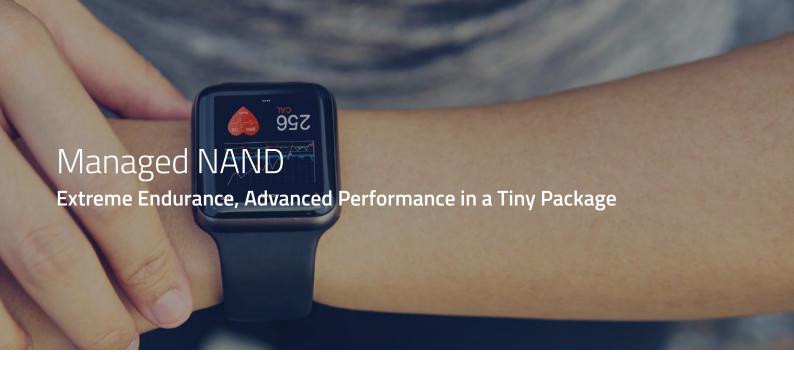
# **TSE Storage Solutions**

- Compliant with the requirements of the BSI TR-03153, Common Criteria PP-SMAERS, PP-CSP
  - Projected Certificate Validity: Up to 8 years (also available with 5-year validity)
- Form Factors: microSD, SD, USB
- \* May vary on payload size (s)

- Capacities: 8 GB and 16 GB
- Data Retention: Up to 10 years (depending on test conditions)
- Lifetime: 20 million signatures\*
- OS Support: Windows, Android, Linux

Product Name	TSE Storage Solutions
Product Line	SecurStor
Flash Type	MLC
Density	8 GB / 16 GB
Performance Signature time	<150 ms
Interface	UHS-I
Operating Temperature	-25°C to 85°C
Reliability MTBF @ 25°C	>2,000,000 hours
Reliability Number of Insertions	10,000
Dimensions (mm)	15.0 x 11.0 x 1.0





ATP's managed NAND solutions integrate raw NAND flash memory and hardware controller. As soldered-down solutions, they are secure against constant vibrations, making them ideal for embedded and automotive applications requiring rugged endurance and durability.

Integrated circuits (IC) package customization service is enabled by ATP's process ownership. Legacy land grid array (LGA) package support is available from 3 to 5 years. ATP also offers packaging flexibility:

- Package sizes (9x10, 11.5x13, 12x18 mm)
- Package forms (100-/132-ball BGA, LGA)
- Die packages (octa-die or higher)



e.MMC offerings use a 153-ball fine pitch ball grid array (FBGA package). Smaller than a typical postage stamp, its tiny footprint makes the e.MMC perfectly suitable for embedded systems with space constraints but require rugged endurance, reliability and durability in harsh environments.

# **Key Differentiators\***

- Extreme Endurance:\*\* 2-3X Higher than standard e.MMC for higher terabytes written (TBW), healthy memory storage, and long product service life.
- SRAM Soft Error Detection and Recovery.\*\*\* Maximizes
  data integrity by providing timely error detection, logging,
  and configurable action to address the error.
- Product Traceability. Laser imprints important information on the ATP e.MMC to identify each piece for accurate tracking and efficient inventory management.
- May vary by product and project support.
- \*\* Under best write amplification index (WAI) with highest sequential write value. May vary by density, test configuration, workload and applications.
- \*\*\* Configuration is predetermined by the customer with ATP and cannot be changed on the field.



NVMe Heat Sink Ball Grid Array (HSBGA) SSDs are ATP's tiniest NVMe flash storage solutions. They use high-speed PCle 3.0 interface x4 lanes and NVMe protocol to deliver up to 32 Gb/s bandwidth at 8 Gb/s per lane.

# **Key Differentiators\***

- **pSLC Mode.** Storing only one bit per cell increases endurance and reliability, offering 2X-3X better sustainable performance.
- Optimized Power Consumption. Consuming low power at only 5 mW duringPower State 4 (Sleep Mode) to deliver huge power savings.
- DRAM-Less Configuration. Host Memory Buffer (HMB) support improves performance by obtaining DRAM resources as cache, thus overcoming the limited memory capacity within the storage and optimizing I/O performance.
- Better Thermal Dissipation. The heat sink effectively transfers heat to cool the device and keep the performance at optimal levels.
- Optional Security Features: HW Write Protect, HW Quick Erase, HW Secure Erase (Data Sanitization, AFSSI-5020), AES-256 Encryption, TCG Opal 2.0

# e.MMC

- AEC-Q100 Grade 2
   (-40°C~105°C) Compliant\*
   AEC-Q100 Grade 3
   (-40°C~85°C) Compliant\*
   Extra-high endurance: 2-3X higher than standard e.MMC\*
- Complies with JEDEC e.MMC v5.1 Standard (JESD84-B51)
   153-ball FBGA (RoHS compliant, "green package")
- LDPC ECC engine\*





				e.M	IMC				
	Extended Ind	ustrial Grade	Automotiv	re Grade 2	Automo	tive Grade 3		Industrial Grade	
Product Line	Premium								
Froduct Line	E700Pa	E600Sa	E700Paa	E600Saa	E700Pia	E600Sia	E750Pi	E700Pi	E700Pi
Flash Type	3D MLC (pSLC mode)	3D MLC	3D MLC (pSLC mode)	3D MLC	3D MLC (pSLC mode	3D MLC	3D TLC (pSLC mode)	3D MLC (pSLC mode	3D TLC (pSLC mode)
IC Package				153-ba	II FBGA				
JEDEC Specification				v5.1, l	HS400				
Power Loss Protection Options				Firmwar	re Based				
Operating Temperature	-40°C to	105°C	-40°C t	o 105°C	-40°C to	85°C		-40°C to 85°C	
Capacity'	8 GB to 64 GB	16 GB to 128 GB	8 GB to 64 GB	16 GB to 128 GB	8 GB to 64 GB	16 GB to 128 GB	10 GB to 21 GB	8 GB to 64 GB	10 GB to 40 GB
				Perfor	mance				
Sequential Read/ Write up to (MB/s) (Max.)"	. 300 / 240	300 / 170	300 / 240	300 / 170	300 / 240	300 / 170	295/ 215	300 / 240	290 / 225
Bus Speed Modes				x1/x	(4 / x8				
ICC (Typical RMS in Read/Write) mA (Max.)	145 / 175	125 / 175	145 / 175	125 / 175	145 / 175	125 / 175	95.5 / 92	145 / 175	100 / 110
ICCQ (Typical RMS in Read/Write) mA (Max.)	120 / 100	115 / 95	120 / 100	115 / 95	110 / 95	115 / 95	104 / 87.5	120 / 100	105 / 100
				Endurance a	nd Reliability				
Endurance TBW** (Max.)	1,213 TB	309 TB	1,213 TB	309 TB	1,320 TB	824 TB	1,034 TB	1,320 TB	1,364 TB
Reliability MTBF @ 25°C				>2,000,0	00 hours				
		Others							
Dimensions (mm)		11.5 x 13.0 x 1.3							
Certifications				AEC-Q100, F	RoHS, REACH			RoHS,	REACH
Warranty				One	Year				

e.MMC										
		Industrial Grade			Commercial Grade					
Product Line					nium					
Product Line	E650Si	E600Si	E600Si	E750Pc	E700Pc	E650Sc	E600Vc	E600Vc		
Flash Type	3D TLC	3D MLC	3D TLC	3D TLC (pS	LC mode)	3D TLC	3D	TLC		
IC Package			153-ե	oall FBGA						
JEDEC Specification			v5.1,	HS400						
Power Loss Protection Options			Firmwa	are Based						
Operating Temperature		-40°C to 85°C				-25°C to 85°C				
Capacity*	32 GB to 64 GB	16 GB to 128 GB	32 GB to 128 GB	10 GB to 21 GB	10 GB to 40 GB	32 GB to 64 GB	32 GB to 128 GB	32 GB		
			Perf	ormance						
Sequential Read/ Write up to (MB/s)**	270 / 215	300 / 170	290 / 225	295 / 215	290 / 225	270 / 215	290 / 225	250 / 135		
Bus Speed Modes			x1 / x4 / x8							
ICC (Typical RMS in Read/Write) mA (Max.)	69.5 / 68.5	125 / 175	100 / 110	95.5 / 92	100 / 110	69.5 / 68.5	100 / 110	81.5 / 49.5		
ICCQ (Typical RMS in Read/Write) mA (Max.)	88 / 85.5	110 / 100	105 / 100	104 / 87.5	105 / 100	88 / 85.5	105 / 100	80.5 / 61.5		
			Endurance	and Reliability						
Endurance TBW** (Max.)	70 TB	824 TB	52 TB	1,034 TB	1,364 TB	70 TB	52 TB	8.3 TB		
Reliability MTBF @ 25°C			>2,000,0	000 hours						
			(	Others						
Dimensions (mm)			11.5 x 1	13.0 x 1.0				9.0 x 10.0 x 0.8		
Certifications			RoH!	S, REACH						
Warranty			One	e Year						

Technologies & Add-On Services***	<b>&amp;</b>	( <del>þ</del> )		<u>1,0</u>		<b>©</b>	\$   <del>-</del> 6		\$\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	SiP			(Ting)
Premium	0	0	0	0	0	0	0	0	0	0	0	0	<b>A</b>
Superior	0	0	0	0	0	0	0	0	0	0	0	0	<b>A</b>
Value	0	0	0	0	0	0	0	0	<b>A</b>	0	0	0	<b>A</b>

<sup>\*</sup> Low-density parity-check error correcting code. By product support.

\*\* All performance is collected or measured using ATP proprietary test environment, without file system overhead.

\*\*\* Please refer to pages 56-58. 

\*: Customization option available on a project basis.

# PCIe® Gen 3 NVMe M.2 Type 1620 HSBGA SSD

- PCle Gen3 x4, NVMe 1.3, M.2 Type 1620
- pSLC mode with 2X-3X of Sustainable Performance\*
- High/Stable performance with Optimized Thermal Throttling Firmware/Heatsink (HSBGA)
- Optimized Power Consumption: 5 mW during Power State 4
- DRAM-less configuration supporting Host Memory Buffer (HMB)\*
- Optional Security features available\*\*
- \* Under highest Sequential write value. May vary by density, configuration, and applications.
- \*\* Customization available on a project basis



	PC	le® Gen 3 NVMe M.2 Type 1620 HSE	BGA SSD					
	Pren							
Product Line	N700Pi	N700Pc	N600Vi	N600Vc				
Interface		PCIe	G3 x4					
Flash Type	3D TLC (ps	SLC mode)	3D -	TLC				
Form Factor		291-Ball	I, HSBGA					
Operating Temperature (Tcase)¹	-40°C to 85°C	0°C to 70°C	-40°C to 85°C	0°C to 70°C				
Power Loss Protection Options		Firmwai	re Based					
Optional SED Features	AES 256-bit Encry	ption, TCG Opal 2.0	-					
Capacity	40 GB to	160 GB	120 GB to 480 GB					
		Perform	mance					
Sequential Read (MB/s) up to	2,0	000	2,0	50				
Sequential Write (MB/s) up to	1,6	500	1,550					
Random Reads IOPS up to	135,	600	138,000					
Random Writes IOPS up to	112,	,000	112,600					
		Endurance ar	nd Reliability					
Endurance (TBW) <sup>2</sup> up to	4,28	0 TB	768	ТВ				
Reliability MTBF @ 25°C		>2,000,000 hours						
	Others							
Dimensions (mm)	16.0 x 20.0 x 1.6							
Certifications		RoHS, F	REACH					
Warranty		1 y	ear					

Technologies & Add-On Services³	<u></u>	(\$)	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	<u>1, 1, 1</u>		١	\$\[\frac{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi_{\chi\tiny{\chi_{\chi_{\chi_{\chi}\tinm\\chi_{\chi_{\chi_{\chi}\chi_{\chi_{\chi}\chi_{\chi}\chi_{\chi\tiny{\chi_{\chi\tiny{\chi_{\chi\tiny{\chi}\tiny{\chi_{\chi}\chi_{\chi}\chi\tin\chi_{\chi\tiny{\chi}\tinm\chi\tiny{\chi\tiny{\chi}\tiny{\chi\tiny{\chi\tiny{\chi\tiny{\chi}\tiny{\chi}\tiny{\chi\tiny{\chi\tiny{\chi\tiny{\chi}\tiny{\chi}\tiny{\chi}\tiny{\chi}\tiny{\chi\tiny{\chi\tiny{\chi\tiny{\chi\tiny{\chi\tiny{\chi\tiny{\chi}\tiny{\chi}\tiny{\chi}\tin}\chi\tiny{\chi\tiny{\chi\tiny{\chi\tiny\tiny{\chi\tiny{\chi\tin\tiny{\chi\tiny{\chi}\tiny{\chi\tiny{\chi\tiny{\chi\tiny{\chi}\tiny{\chi\tiny{\chi\tiny{\chi\tiny{\chi}\chi\tiny{\chi\tin\tiny\tin\tin\tin\tin\tin\chi\tiny{\chi\tin\tin\tin\tin\tin\tin\tii\tin\tin\ti		8	######################################	SiP		(Time)
	0	0	0	0	0	0	0	<b>A</b>	<b>A</b>	<b>A</b>	0	0	<b>A</b>
	0	0	0	0	0	0	_	-	-	0	0	0	_

# Flash Products Naming Rule



#### **Premium Line**

The ATP Premium Line consists of mass storage solutions built for uncompromising performance, maximum dependability, and exceptional endurance. Outfitted with best-in-class technologies ensuring the highest levels of reliability, these solutions are hardwired for the most demanding mission-critical applications where system failures or interruptions can significantly impact operations. With industrial temperature ratings of -40°C to 85°C, these rugged solutions can withstand harsh operating environments and extreme temperatures. Unparalleled usage life and brisk write speeds set the Premium Line a cut above the rest. High input/output operations per second (IOPS) ensure consistently high performance, and ATP's power loss protection technology guarantees that data in transit are safely stored to the flash chip in the event of a power loss, thus safeguarding data integrity, averting data loss or corruption, and preventing device damage.

# **Superior Line**

The ATP Superior Line brings together powerful and proven features and technologies for rigorous operations in diverse industries, capably handling mixed workloads with high IOPS requirements. Generous storage densities make these products ideal for data-hungry and write-intensive applications; mid-density drive options offer a wider range of choices for cost efficiency; and, configurable over-provisioning gives users flexibility to make adjustments based on actual workloads for the optimal balance between drive performance and endurance. ATP Superior Line products are available in both industrial temperature (-40°C to 85°C) and commercial temperature ratings (embedded SSD: 0°C to 70°C; SD/microSD card: -25°C to 85°C), so users can choose the temperature range most appropriate for their needs.

#### Value Line

The ATP Value Line integrates advanced essential solutions to the growing needs of enterprises and industries, offering sustained, reliable performance and consistent reliability. Superb choices as embedded boot or boot image devices, they are ideally suited for Internet of Things (IoT) applications, spurring greater connectivity for homes, cars, medical equipment, and other smart devices. Ample storage capacity is available for installing an operating system with space to spare for other applications.

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#### **Automotive Edition**

The ATP Automotive Edition consists of tailor-made solutions to meet automotive customers' requirements for maximum data reliability. These solutions undergo the strictest levels of testing and are certified according to automotive-industry standards, including but not limited to IATF 16949 Certification, APQP, PPAP, IMDS, AEC-Q100, product selection/features and joint validation tests depending on project support and according to customer request.

# Solutions & Technologies

As a technology-driven company, ATP is committed to developing innovative solutions and harnessing the most advanced technologies to ensure that our products deliver the highest levels of data integrity, reliability and retention for mission-critical applications.



#### Life Monitor/S.M.A.R.T.\*

Provides a user-friendly interface for monitoring the health status and life expectancy of a flash product.



#### • Hardware-based Power Loss Protection

This hardware-based power failure protection prevents data loss during a power loss event by ensuring that the last read/write/erase command is completed, and data is stored safely in non-volatile flash memory. Select NVMe modules and SATA SSDs feature a new microcontroller unit (MCU)-based design that allows the PLP array to perform intelligently in various temperatures, power glitches and charge states to protect both device and data.



# · Advanced Wear Leveling

Manages the reads and writes across blocks evenly to optimize the overall life expectancy of a flash product.



#### • End-to-End Data Path Protection

Ensures error checking and correction as data moves from the host to the storage device controller and vice versa. By covering the entire data path, end-to-end protection guarantees integrity at any point during data transfer.

- \* Compatibility and support may vary by platform or operating system.
- Flash solutions
- DRAM solutions
- Flash/DRAM solutions
- → Value-added solutions



#### AutoRefresh

Monitors the error bit level in every operation. Before the error bit in a block reaches or exceeds the preset threshold value, AutoRefresh moves the data to a healthy block, thus preventing the controller from reading blocks with too many error bits and averting read disturbance and data corruption.



# • Firmware-based Power Loss Protection

The firmware-based power failure protection effectively protects data written to the device prior to power loss. After the host receives a signal from the device that the WRITE operation has been successfully completed, newly written as well as previously written data are protected even if a sudden power loss occurs.



#### • Dynamic Data Refresh

Runs automatically in the background to reduce the risk of read disturbance and sustain data integrity in seldom-accessed areas by sequentially scanning the user area flag record without affecting the read/write operation. The data that has been completely moved to another block will be read and compared with the source data to ensure data integrity.



#### Auto-Read Calibration

As program/erase (P/E) cycles increase, memory cells age and cause voltage shifts that lead to high bit error rates (BER) when predefined read thresholds are fixed. The Auto-Read Calibration (ARC) function reduces BER and enhances reliability by adjusting/calibrating the read thresholds. ARC is supported by the TLC LDPC controller.



#### Secure Erase

A sanitization solution made especially for SSDs and memory cards making sure that sensitive data is not recovered or retrieved if the SSD or memory card needs to be disposed or repurposed. By making sure that no remnant of sensitive data remains, Secure Erase is the ideal solution for government and business applications with intense security requirements.



### • Dynamic Thermal Throttling

This mechanism provides a delicate balance between performance and temperature instead of dramatic performance reduction. Temperature sensors continuously detect the device temperature. After sophisticated FW transactions, the performance gradually declines, and the temperature is adjusted.



#### ■ Wide Temp DRAM Modules

These modules use unique ATP testing and technologies to enable support for industrial temperature operating ranges from -40°C to 85°C but at lower price points than modules with native industrial grade ICs.



# • SiP (System in Package)

Manufacturing process that encapsulates all exposed components to provide protection and shielding.



# • TCG Opal 2.0

TCG Opal Security Subsystem Class (SSC) 2.0 is a set of specifications for self-encrypting drives that present a hierarchy of security management standards to secure data from theft and tampering. Security features include hardware-based data encryption, pre-boot authentication (PBA) and AES-128/256 data encryption to protect the confidentiality of data at rest.



#### • Industrial Temperature

Operational stability in extreme temperatures from -40°C to 85°C.



#### Vibration-Proof BGA Package

Soldered-down solutions can withstand vigorous shaking and are resistant against vibrations for reliable performance even during grueling operations.



# Anti-Sulfur Resistors

ATP DRAM modules and NAND flash storage products offer an anti-sulfur resistor option to prevent the corrosive effects of sulfur contamination, guaranteeing continued dependable performance for a long time.



### Conformal Coating

Protects electronic circuits with a coating of the chemical compound Parylene to resist dust, chemical contaminants, extreme temperature, moisture and corrosion.



# Chamfering PCB Design

Chamfering refers to the process of "beveling or tapering" the connector edges for easier insertion into the memory slots. The bevel is done at specific angles, typically at around 40° to 50°.



# ■ Thicker Gold Finger

 $30\mu''$ -thick gold plating of the DRAM contact optimizes signal transmission quality between the connector and DRAM modules.



# Complete Drive Test 1

For NAND flash storage products, the entire drive, including firmware, user and spare areas, is thoroughly tested to ensure that there are no bad blocks. DRAM products also undergo complete testing, covering PHY and controller, including meta/mapping and data caching areas.



#### Joint Validation

ATP conducts compatibility/function tests with client-supplied host devices and systems, to proactively detect and minimize failures that may not be caught in production tests, thus improving overall quality.



# ■ Test During Burn-In (TDBI)

TDBI involves subjecting ATP DRAM modules to various temperatures, power cycling, voltages and other stress conditions within a certain period. It aims to cause weak ICs to fail so they can be screened out, thus making sure that the modules contain only the most robust ICs.

- \* Compatibility and support may vary by platform or operating system.
- Flash solutions
- DRAM solutions
- ◆ Flash/DRAM solutions
- → Value-added solutions

Form Factor	Product Line	Life Monitor/ S.M.A.R.T.	Firmware-based Power Loss Protection	Hardware-based Power Loss Protection	AutoRefresh	Advanced Wear Leveling	Dynamic Data Refresh	End-to-End Data Path Protection	Auto-Read Calibration	Secure Erase	TCG Opal 2.0	Dynamic Thermal Throttling	Industrial Temperature	SiBiF	Vibration-Proof BGA Package	Anti-Sulfur Resistors	Conformal Coating	Complete Drive Test	Joint Validation
PCIe <sup>®</sup> Gen 4 NVMe M.2 2280 SSD ( 240 GB to 1920 GB)	Superior	0	0	0	0	0	0	0	0	<b>A</b>	<b>A</b>	_	0	_	_	<b>A</b>	<b>A</b>	_	_
PCIe® Gen4 High-Capacity NVMe M.2 2280 SSD (3.84 TB)	Superior	0	0	_	0	0	0	0	0	<b>A</b>	<b>A</b>	_	0	_	_	<b>A</b>	<b>A</b>	_	_
	Premium	0	0	0	0	0	0	0	0	<b>A</b>	0	_	0	_	_	<b>A</b>	<b>A</b>	_	_
PCle® Gen 3 NVMe M.2 2280 / 2242 / 2230 SSD	Superior	0	0	0	0	0	0	0	0	<b>A</b>	0	_	<b>A</b>	_	-	<b>A</b>	<b>A</b>	_	_
	Value	0	0	_	0	0	0	0	0	_	_	_	_	_	_	•	<b>A</b>	_	_
PCIe® Gen3 High-Capacity NVMe M.2 2280 SSD	Superior	0	0	_	0	0	0	0	0	<b>A</b>	<b>A</b>	0	0	_	_	_	<b>A</b>	_	<b>A</b>
PCIe® Gen4 NVMe U.2 SSD	Superior	0	0	0	0	0	0	0	0	<b>A</b>	<b>A</b>	_	0	_	_	•	<b>A</b>	_	<b>A</b>
PCIe® Gen3 NVMe U.2 SSD	Superior	0	0	0	0	0	0	0	0	0	0	0	0	_	_	_	<b>A</b>	_	<b>A</b>
	Premium	0	0	0	0	0	0	0	0	<b>A</b>	0	_	0	_	_	<b>A</b>	<b>A</b>	_	_
SATA III M.2 2280 / 2242 SSD	Superior	0	0	0	0	0	0	0	0	<b>A</b>	0	_	<b>A</b>	_	_	<b>A</b>	•	_	_
	Value	0	0	_	0	0	0	_	0	-	_	_	_	_	_	-	_	_	_
	Premium	0	0	0	0	0	0	_	0	<b>A</b>	0	_	0	_	_	<b>A</b>	<b>A</b>	_	_
SATA III 2.5" SSD	Superior	0	0	0	0	0	0	_	0	<b>A</b>	0	_	<b>A</b>	_	_	<b>A</b>	<b>A</b>	_	_
	Value	0	0	_	0	0	0	-	0	-	_	_	_	_	_	-	-	_	_
	Premium	0	0	0	0	0	0	-	0	<b>A</b>	0	_	0	_	_	<b>A</b>	<b>A</b>	_	_
SATA III mSATA SSD	Superior	0	0	0	0	0	0	_	0	<b>A</b>	0	_	<b>A</b>	_	_	<b>A</b>	<b>A</b>	_	_
	Value	0	0	_	0	0	0	-	-	_	-	_	_	_	_	-	_	_	_
USB 3.2 NANODURA Dual	Superior	0	0	_	_	0	-	_	-	_	_	_	_	0	-	-	-	_	_
USD a c NANODUDA	Premium	0	0	_	_	0	-	-	-	_	_	_	0	0	_	-	-	_	_
USB 2.0 NANODURA	Superior	0	0	_	_	0	_	_	_	_	_	_	_	0	_	-	_	_	_
	Premium	0	0	<b>A</b>	_	0	-	_	-	_		_	0	-	_	<b>A</b>	<b>A</b>	_	_
USB 2.0 eUSB	Superior	0	0	<b>A</b>	_	0	_	_	_	_	_	_	_	_	_	<b>A</b>	<b>A</b>	_	_
(micro)SD/(micro)SDHC/	Premium	<b>A</b>	0	_	0	0	•	-	_	0	_	_	0	0	_	-	_	0	<b>A</b>
(micro)SDXC Card	Superior	<b>A</b>	0	_	0	0	0	_	<b>A</b>	0	_	_	<b>A</b>	0	_	_	_	0	<b>A</b>
PCIe® Gen4 NVMe CFexpress Card	Superior	0	0	_	0	0	0	0	0	<b>A</b>	<b>A</b>	_	0	_	-	<b>A</b>	<b>A</b>	0	<b>A</b>
Cfast Card	Premium	0	0	<b>A</b>	0	0	0	-	-	0	-	-	0	-	-	<b>A</b>	<b>A</b>	_	_
	Premium	0	0	0	0	0	0	_	_	_	_	_	0	_	_	<b>A</b>	<b>A</b>	_	_
Compact Flash Card	Superior	0	0	_	0	0	0	_	_	_	_	_	_	_	-	<b>A</b>	<b>A</b>	_	_
	Premium	0	0	_	0	0	0	0	0	0	_	_	0	0	0	_	_	0	<b>A</b>
e.MMC	Superior	0	0	_	0	0	0	0	0	0	_	_	0	0	0	-	_	0	<b>A</b>
	Value	0	0	_	0	0	0	0	0	0	_	_	<b>A</b>	0	0	-	_	0	<b>A</b>
PCIe® Gen 3 NVMe M.2	Premium	0	0	_	0	0	0	0	0	<b>A</b>	<b>A</b>	-	<b>A</b>	0	0	-	-	_	<b>A</b>
Type 1620 HSBGA SSD	Value	0	0	_	0	0	0	0	_	_	_	_	0	0	0	_	_	_	_

# Complete Flash Portfolio

Form Factor	Product Line Naming	Interface	Capacity	NAND	Reliability TBW (max) * _	Sequential F MB/s		Operating Temperature (°C)
					Tor (max)	Read	Write	
PCIe® Gen4 NVMe M.2 2280 SSD	N600Si / N600Sc	PCIe G4 x4	240 GB to 3.84 TB	3D TLC	11,400	6,450	6,000	-40 to 85 / 0 to 70
	N750Pi	PCIe G3 x4	40 GB to 320 GB	3D TLC (pSLC mode)	16,000	3,150	2,670	-40 to 85
	N700Pi	PCIe G3 x4	40 GB to 640 GB	3D TLC (pSLC mode)	21,300	3,150	2,820	-40 to 85
	N650Si / N650Sc	PCIe G3 x4	120 GB to 960 GB	3D TLC	4,640	3,420	3,050	-40 to 85 / 0 to 70
M.2 2280 SSD	N600Si / N600Sc	PCIe G3 x4	120 GB to 3.84 TB	3D TLC	10,600	3,420	3,050	-40 to 85 / 0 to 70
	N600Vc	PCIe G3 x4	120 GB to 960 GB	3D TLC	1,520	2,600	1,870	0 to 70
	A750Pi	SATA 6Gb/s	80 GB to 320 GB	3D TLC (pSLC mode)	19,200	560	520	-40 to 85
	A700Pi	SATA 6Gb/s	80 GB to 320 GB	3D TLC (pSLC mode)	12,800	560	520	-40 to 85
SATA III M.2 2280 SSD	A650Si / A650Sc	SATA 6Gb/s	120 GB to 960 GB	3D TLC	4,655	560	480	-40 to 85 / 0 to 70
	A600Si / A600Sc	SATA 6Gb/s	120 GB to 960 GB	3D TLC	2,792	560	510	-40 to 85 / 0 to 70
	A600Vc	SATA 6Gb/s	32 GB to 1 TB	3D TLC	1,530	560	525	0 to 70
PCle® Gen3 NVMe M.2 2242 SSD	N600Vc	PCIe G3x4	120 GB to 960 GB	3D TLC	1,520	2,600	1,870	0 to 70
	A800Pi	SATA 6Gb/s	8 GB to 64 GB	SLC	5,333	530	400	-40 to 85
	A750Pi	SATA 6Gb/s	40 GB to 160 GB	3D TLC (pSLC mode)	9,600	560	520	-40 to 85
SATA III	A700Pi	SATA 6Gb/s	40 GB to 160 GB	3D TLC (pSLC mode)	6,400	560	520	-40 to 85
M.2 2242 SSD	A650Si / A650Sc	SATA 6Gb/s	120 GB to 480 GB	3D TLC	2,327	560	480	-40 to 85 / 0 to 70
	A600Si / A600Sc	SATA 6Gb/s	120 GB to 480 GB	3D TLC	1,396	560	510	-40 to 85 / 0 to 70
	A600Vc	SATA 6Gb/s	32 GB to 1 TB	3D TLC	1,530	560	525	0 to 70
PCIe® Gen3 NVMe	N700Si / N700Sc	PCIe G3 x4	40 GB to 160 GB	3D TLC (pSLC mode)	4,280	2,000	1,600	-40 to 85 / 0 to 70
M.2 2230 SSD	N600Vi / N600Vc	PCIe G3 x4	120 GB to 480 GB	3D TLC	768	2,050	1,550	-40 to 85 / 0 to 70
PCIe® Gen4 NVMe U.2 SSD	N600Si / N600Sc	PCIe G4 x4	960 GB to 7.68 TB	3D TLC	22,800	3,900	3,800	-40 to 85 / 0 to 70
PCle® Gen3 NVMe U.2 SSD	N600Si	PCIe G3 x4	960 GB to 7.68 TB	3D TLC	21,000	3,100	1,400	-40 to 85
	A800Pi	SATA 6Gb/s	8 GB to 256 GB	SLC	21,333	520	420	-40 to 85
	A750Pi	SATA 6Gb/s	80 GB to 640 GB	3D TLC (pSLC mode)	38,400	560	520	-40 to 85
SATA III 2.5" SSD	A700Pi	SATA 6Gb/s	80 GB to 640 GB	3D TLC (pSLC mode)	25,600	560	520	-40 to 85
	A650Si / A650Sc	SATA 6Gb/s	120 GB to 1,920 GB	3D TLC	9,310	560	520	-40 to 85 / 0 to 70
	A600Si / A600Sc	SATA 6Gb/s	120 GB to 1,920 GB	3D TLC	5,585	560	520	-40 to 85 / 0 to 70
	A600Vc	SATA 6Gb/s	32 GB to 1 TB	3D TLC	1,530	560	525	0 to 70
	A800Pi	SATA 6Gb/s	8 GB to 128 GB	SLC	10,667	530	430	-40 to 85
	A750Pi	SATA 6Gb/s	40 GB to 160 GB	3D TLC (pSLC mode)	9,600	560	520	-40 to 85
SATA III	A700Pi	SATA 6Gb/s	40 GB to 160 GB	3D TLC (pSLC mode)	6,400	560	520	-40 to 85
mSATA SSD	A650Si / A650Sc	SATA 6Gb/s	120 GB to 480 GB	3D TLC	2,327	560	480	-40 to 85 / 0 to 70
	A600Si / A600Sc	SATA 6Gb/s	120 GB to 480 GB	3D TLC	1,396	560	510	-40 to 85 / 0 to 70
	A600Vc	SATA 6Gb/s	32 GB to 1 TB	3D TLC	1,530	560	525	0 to 70
USB 3.2 NANODURA Dual	B600Sc	USB 3.2	32 GB to 128 GB	3D TLC	84	270	85	0 to 70
USB 2.0	B800Pi	USB 2.0	512 MB to 8 GB	SLC	192	31	21	-40 to 85
NANODURA	B600Sc	USB 2.0	4 GB to 8 GB	MLC	9.6	26	10	0 to 70
USB 2.0	B800Pi	USB 2.0	1 GB to 32 GB	SLC	1,584	36	25	-40 to 85
eUSB	B600Sc	USB 2.0	8 GB to 32 GB	MLC	38.4	25	19	0 to 70

 $<sup>^{\</sup>ast}$  Under highest Sequential write value. May vary by density, configuration and applications.

Form Factor	Product Line Naming	Interface	Capacity	NAND	Reliability TBW (max) *	Sequential P MB/s (		Operating Temperature (°C)
	8					Read	Write	( 2 /
	S800Pi	HS mode / UHS-I	512 MB to 8 GB	SLC	192	68	39	-40 to 85
	S750Pi / S750Sc	UHS-I	8 GB to 32 GB	3D TLC (pSLC mode)	1,745	99	82	-40 to 85 / -25 to 85
	S700Pi / S700Sc	UHS-I	8 GB to 64 GB	3D TLC (pSLC mode)	1,164	95	70	-40 to 85 / -25 to 85
SD/ SDHC/	S650Si / S650Sc	UHS-I	32 GB to 128 GB	3D TLC	582	96	57	-40 to 85 / -25 to 85
SDXC Card	S600Si	UHS-I	32 GB to 512 GB	3D TLC	1,396	96	66	-40 to 85
	S600Sc	UHS-I	8 GB to 16 GB	MLC	19	68	23	-25 to 85
	S600Sia / Sca	UHS-I	8 GB to 64 GB	MLC / 3D TLC	307	96	65	-40 to 85 / -25 to 85
	S600Sc	UHS-I	32 GB to 512 GB	3D TLC	1,396	96	66	-25 to 85
	S800Pi	HS mode / UHS-I	512 MB to 8 GB	SLC	192	68	39	-40 to 85
	S750Pi / S750Sc	UHS-I	8 GB to 64 GB	3D TLC (pSLC mode)	3,490	99	82	-40 to 85 / -25 to 85
	S700Pi / S700Sc	UHS-I	8 GB to 64 GB	3D TLC (pSLC mode)	1,164	95	70	-40 to 85 / -25 to 85
microSD/ microSDHC/	S650Si / S650Sc	UHS-I	32 GB to 256 GB	3D TLC	1,164	99	59	-40 to 85 / -25 to 85
microSDXC Card	S600Si	UHS-I	32 GB to 512 GB	3D TLC	1,396	96	66	-40 to 85
	S600Sc UHS-I		8 GB to 32 GB	MLC	38	68	24	-25 to 85
	S600Sc	UHS-I	32 GB to 512 GB	3D TLC	1,396	96	66	-25 to 85

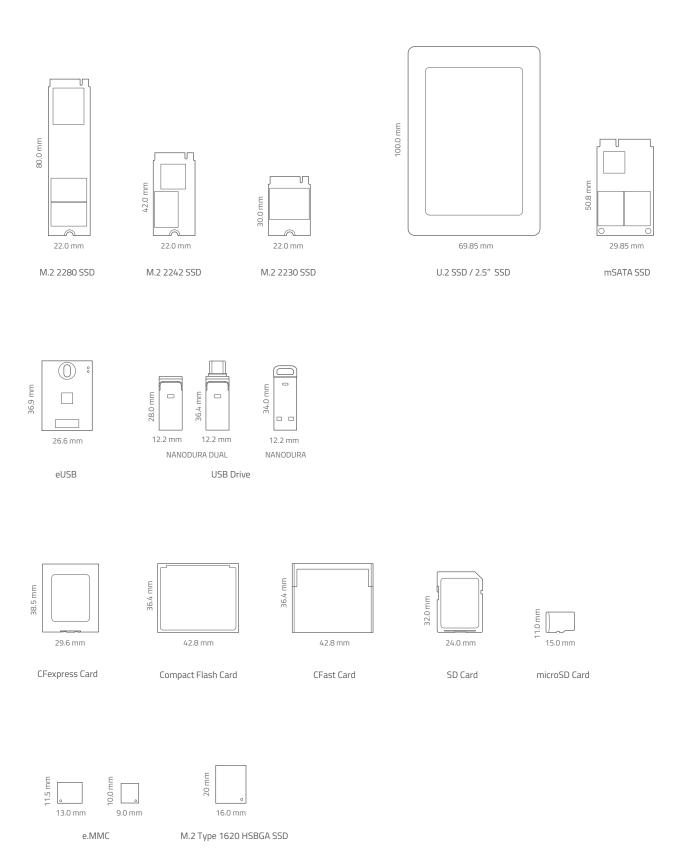
Form Factor	Product Line Naming	Interface	Capacity	NAND	Reliability TBW (max) *	Sequential P MB/s (		Operating Temperature (°C)	
	IVAIIIIII B				I DVV (IIIax)	Read	Write	(2)	
PCIe® Gen4 NVMe CFexpress Card	N600Si / N600Sc	PCIe G4 x2	128 GB to 1 TB	3D TLC	1,000	3,500	3,100	-40 to 85 / 0 to 70	
CFast Card	A800Pi	SATA 6Gb/s	8 GB to 32 GB	SLC	2,667	500	300	-40 to 85	
	1800Pi	UDMA 0~4	512 MB to 32 GB	SLC	1,280	61	55	-40 to 85	
CompactFlash Card	1700Sc	UDMA 0~6	8 GB to 16 GB	Pseudo SLC	128	110	80	0 to 70	
	1600Sc	UDMA 0~6	16 GB to 32 GB	MLC	38	108	46	0 to 70	

 $<sup>^{\</sup>ast}$  Under highest Sequential write value. May vary by density, configuration and applications.

Form Factor	Product Line Naming	Interface	Capacity	NAND	Reliability TBW (max) *	Sequential P MB/s		Operating Temperature (°C)
	, warming				1 Doo (max)	Read	Write	
	E700Pa	v5.1, HS400	8 GB to 64 GB	3D MLC (pSLC mode)	1,213	300	240	-40 to 105
	E600Sa	v5.1, HS400	16 GB to 128 GB	3D MLC	309	300	170	-40 to 105
	E700Paa	v5.1, HS400	8 GB to 64 GB	3D MLC (pSLC mode)	1,213	300	240	-40 to 105 (AEC-Q100 Grade 2)
	E600Saa	v5.1, HS400	16 GB to 128 GB	3D MLC	309	300	170	-40 to 105 (AEC-Q100 Grade 2)
	E700Pia	v5.1, HS400	8 GB to 64 GB	3D MLC (pSLC mode)	1,320	300	240	-40 to 85 (AEC-Q100 Grade 3)
	E600Sia	v5.1, HS400	16 GB to 128 GB	3D MLC	824	300	170	-40 to 85 (AEC-Q100 Grade 3)
	E750Pi	v5.1, HS400	10 GB to 21 GB	3D TLC (pSLC mode)	1,034	295	215	-40 to 85
e.MMC	E700Pi	v5.1, HS400	8 GB to 64 GB	3D MLC (pSLC mode)	1,320	300	240	-40 to 85
	E700Pi	v5.1, HS400	10 GB to 40 GB	3D TLC (pSLC mode)	1,364	290	225	-40 to 85
	E650Si	v5.1, HS400	32 GB to 64 GB	3D TLC	70	270	215	-40 to 85
	E600Si	v5.1, HS400	16 GB to 128 GB	3D MLC	824	300	170	-40 to 85
	E600Si	v5.1, HS400	32 GB to 128 GB	3D TLC	52	290	225	-40 to 85
	E750Pc	v5.1, HS400	10 GB to 21 GB	3D TLC (pSLC mode)	1,034	295	215	-25 to 85
	E700Pc	v5.1, HS400	10 GB to 40 GB	3D TLC (pSLC mode)	1,364	290	225	-25 to 85
	E650Sc	v5.1, HS400	32 GB to 64 GB	3D TLC	70	270	215	-25 to 85
	E600Vc	v5.1, HS400	32 GB to 128 GB	3D TLC	52	290	225	-25 to 85
PCle® Gen 3	N700Pi / N700Pc	PCIe G3 x4	40 GB to 160 GB	3D TLC (pSLC mode)	4,280	2,000	1,600	-40 to 85 / 0 to 70
NVMe M.2 Type 1620 HSBGA SSD	N600Vi / N600Vc	PCIe G3 x4	120 GB to 480 GB	3D TLC	768	2,050	1,550	-40 to 85 / 0 to 70

 $<sup>^{\</sup>ast}$  Under highest Sequential write value. May vary by density, configuration and applications.

# Product Dimensions (Size) Comparison



From our humble beginnings with only two desks in a business suite in Silicon Valley, we have established ourselves as global leaders in storage and memory.

Today, over 70% of companies listed on Gartner's Magic Quadrant report for Primary Storage,

Data Center and Cloud Computing, and WAN-Edge Infrastructure consider ATP as a strategic supplier.



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